PCD3350A

Ceibo In-Circuit Emulator Supporting PCD3350A: **DS-48**

http://ceibo.com/eng/products/ds48.shtml

Ceibo Programmer Supporting PCD3350A: **MP-51**

http://ceibo.com/eng/products/mp51.shtml

DATA SHEET

PCD3350A

8-bit microcontroller with DTMF generator, 256 bytes EEPROM and real-time clock

Product specification

Supersedes data of 1996 May 09

File under Integrated Circuits, IC03

1996 Dec 18

**Philips
Semiconductors**

PHILIPS

PHILIPS

**8-bit microcontroller with DTMF generator,
256 bytes EEPROM and real-time clock**   **PCD3350A**

CONTENTS

8-bit microcontroller with DTMF generator, 256 bytes EEPROM and real-time clock

PCD3350A

1 FEATURES

- 8-bit CPU, ROM, RAM, EEPROM, real-time clock and I/O; all in a 44-lead quad flat package
- 8 kbytes ROM
- 256 bytes RAM
- 256 bytes Electrically Erasable Programmable Read Only Memory (EEPROM)
- 32 kHz crystal oscillator for Real-Time Clock (RTC)
- EEPROM programmable RTC
- Over 100 instructions (based on MAB8048) all of 1 or 2 cycles
- 34 quasi-bidirectional I/O port lines
- 8-bit programmable Timer/event counter 1
- 8-bit reloadable Timer 2
- Three single-level vectored interrupts:
  - external
  - 8-bit programmable Timer/event counter 1
  - derivative; triggered by reloadable Timer 2
- Two test inputs, one of which also serves as the external interrupt input
- DTMF, modem, musical tone generator
- Reference for supply and temperature-independent tone output
- Filtering for low output distortion (CEPT compatible)
- Melody output for ringer application
- Programmable DTMF clock divider
- Power-on-reset
- Stop and Idle modes

- Supply voltage: 1.8 to 6 V (DTMF tone output and EEPROM erase/write from 2.5 V)
- CPU clock frequency: 1 to 16 MHz (3.58 MHz or 10.74 MHz for DTMF)
- Operating ambient temperature: −25 to +70 °C
- Manufactured in silicon gate CMOS process.

2 GENERAL DESCRIPTION

This data sheet details the specific properties of the PCD3350A. The shared properties of the PCD33xxA family of microcontrollers are described in the *"PCD33xxA family"* data sheet, which should be read in conjunction with this publication.

The PCD3350A is a microcontroller designed primarily for telephony applications. It includes 8 kbytes ROM, 256 bytes RAM, 34 I/O lines, and an on-chip generator for dual tone multifrequency (DTMF), modem and musical tones. In addition to dialling, the generated frequencies can be made available as square waves for melody generation, providing ringer operation.

The PCD3350A also incorporates 256 bytes of EEPROM, permitting data storage without battery backup. The EEPROM can be used for storing telephone numbers, particularly for implementing redial functions.

Finally, the PCD3350A includes a low power 32 kHz crystal oscillator with an EEPROM programmable Real-Time Clock (RTC) working in standby mode.

The instruction set is similar to that of the MAB8048 and is a sub-set of that listed in the *"PCD33xxA family"* data sheet.

3 ORDERING INFORMATION (see note 1)

TYPE NUMBER	PACKAGE			
	NAME	DESCRIPTION		VERSION
PCD3350AH	QFP44	plastic quad flat package; 44 leads (lead length 2.35 mm); body 14 × 14 × 2.2 mm		SOT205-1

Note

1. Please refer to the Order Entry Form (OEF) for this device for the full type number to use when ordering. This type number will also specify the required program and the ROM mask options.
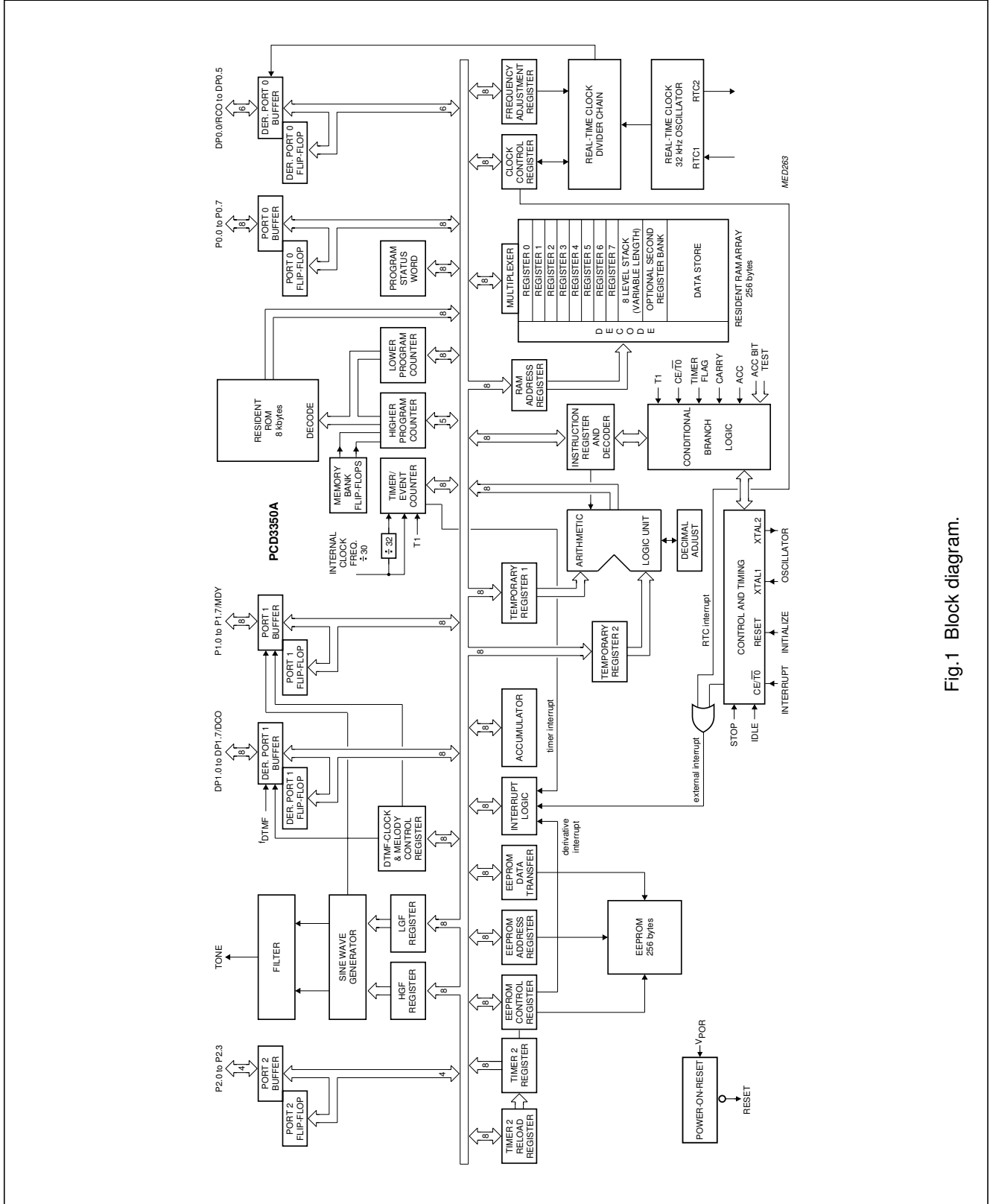
4   BLOCK DIAGRAM

Fig.1 Block diagram.

5 PINNING INFORMATION

5.1 Pinning
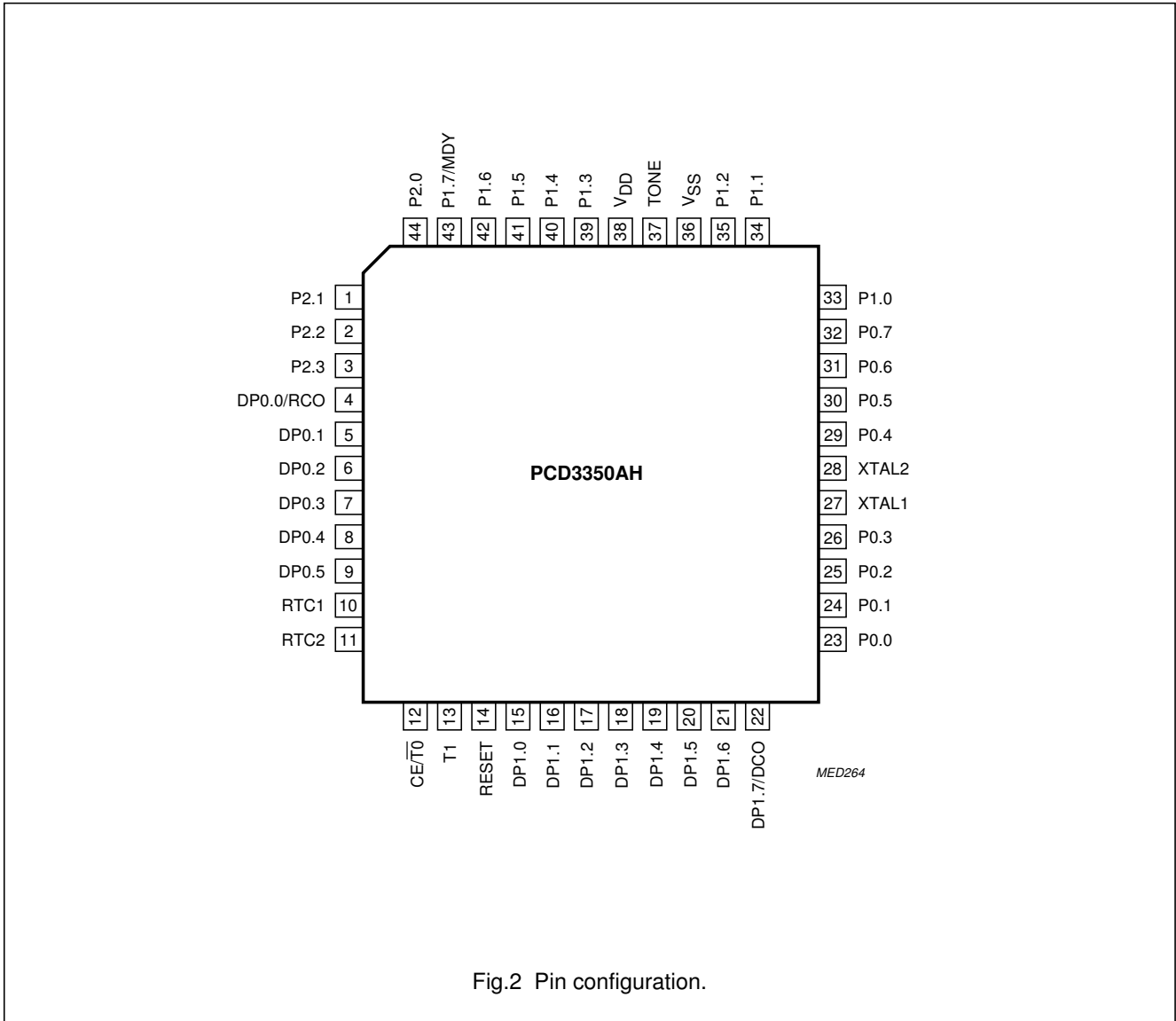
Fig.2 Pin configuration.

5.2 Pin description

Table 1 SOT205-1 package (for information on parallel I/O ports, see Chapter 14)

SYMBOL	PIN	TYPE	DESCRIPTION
P2.1 to P2.3	1 to 3	I/O	3 bits of Port 2: 4-bit quasi-bidirectional I/O port
DP0.0/RCO	4	I/O	1 bit of Derivative Port 0: 6-bit quasi-bidirectional I/O port; or RTC output
DP0.1 to DP0.5	5 to 9	I/O	5 bits of Derivative Port 0: 6-bit quasi-bidirectional I/O port
RTC1	10	I	Real Time Clock 32 kHz oscillator input
RTC2	11	O	Real Time Clock 32 kHz oscillator output
CE/$\overline{\text{T0}}$	12	I	Chip Enable or Test 0 input
T1	13	I	Test 1/count input of 8-bit Timer/event counter 1
RESET	14	I	reset input
DP1.0 to DP1.6	15 to 21	I/O	7 bits of Derivative Port 1: 8-bit quasi-bidirectional I/O port
DP1.7/DCO	22	I/O	1 bit of Derivative Port 1: 8-bit quasi-bidirectional I/O port; or DTMF clock output
P0.0 to P0.3	23 to 26	I/O	4 bits of Port 0: 8-bit quasi-bidirectional I/O port
XTAL1	27	I	crystal oscillator/external clock input
XTAL2	28	O	crystal oscillator output
P0.4 to P0.7	29 to 32	I/O	4 bits of Port 0: 8-bit quasi-bidirectional I/O port
P1.0 to P1.2	33 to 35	I/O	3 bits of Port 1: 8-bit quasi-bidirectional I/O port
V$_{SS}$	36	P	ground
TONE	37	O	DTMF output
V$_{DD}$	38	P	positive supply voltage
P1.3 to P1.6	39 to 42	I/O	4 bits of Port 1: 8-bit quasi-bidirectional I/O port
P1.7/MDY	43	I/O	1 bit of Port 1: 8-bit quasi-bidirectional I/O port; or melody output
P2.0	44	I/O	1 bit of Port 2: 4-bit quasi-bidirectional I/O port

6   FREQUENCY GENERATOR

A versatile frequency generator section with built-in programmable clock divider is provided (see Fig.3). The clock divider allows the DTMF section to run either with the main clock frequency ($f_{DTMF} = f_{xtal}$) or with a third of it ($f_{DTMF} = \frac{1}{3} \times f_{xtal}$) depending on the state of the divider control bit DIV3 (see Table 4). The frequency generator includes precision circuitry for dual tone multifrequency (DTMF) signals, which is typically used for tone dialling telephone sets.

The TONE output can alternatively issue twelve modem frequencies for data rates between 300 and 1200 bits/s.

In addition to DTMF and modem frequencies, two octaves of musical scale in steps of semitones are available. Their frequencies are provided either in purely sinusoidal form on the TONE output or as a square wave on the port line P1.7/MDY. The latter is typically for ringer applications in telephone sets. If no frequency output is selected the TONE output is in 3-state mode.

6.1   Frequency generator derivative registers

6.1.1   HIGH AND LOW GROUP FREQUENCY REGISTERS

Table 2 gives the addresses, symbols and access types of the High Group Frequency (HGF) and Low Group Frequency (LGF) registers, used to set the frequency output.

Table 2   Hexadecimal addresses, symbols, access types and bit symbols of the frequency registers

REGISTER ADDRESS	REGISTER SYMBOL	ACCESS TYPE	BIT SYMBOLS							
			7	6	5	4	3	2	1	0
11H	HGF	W	H7	H6	H5	H4	H3	H2	H1	H0
12H	LGF	W	L7	L6	L5	L4	L3	L2	L1	L0

6.1.2   CLOCK AND MELODY CONTROL REGISTER (MDYCON)

Table 3   Clock and Melody Control Register, MDYCON (address 13H; access type R/W)

7	6	5	4	3	2	1	0
0	0	0	0	0	EDCO	DIV3	EMO

Table 4   Description of MDYCON bits

| BIT	SYMBOL	DESCRIPTION
7 to 3	–	These bits are set to a logic 0.
2	EDCO	Enable DTMF clock output. If bit EDCO = 0, then DP1.7/DCO is a general purpose derivative port line. If bit EDCO = 1, then DP1.7/DCO is the DTMF clock output. EDCO = 1 does not inhibit the port instructions for DP1.7/DCO. Therefore the state of both port line and flip-flop may be read in and the port flip-flop may be written by derivative port instructions. However, the port flip-flop of DP1.7/DCO must remain set to avoid conflicts between DTMF clock and port outputs.
1	DIV3	Enable DTMF clock divider. If bit DIV3 = 0, then the DTMF clock $f_{DTMF} = f_{xtal}$. If bit DIV3 = 1, then $f_{DTMF} = \frac{1}{3} \times f_{xtal}$.
0	EMO	Enable Melody Output. If bit EMO = 0, then P1.7/MDY is a standard port line. If bit EMO = 1, then P1.7/MDY is the melody output. EMO = 1 does not inhibit the port instructions for P1.7/MDY. Therefore the state of both port line and flip-flop may be read in and the port flip-flop may be written by port instructions. However, the port flip-flop of P1.7/MDY must remain set to avoid conflicts between melody and port outputs. When the HGF contents are zero while EMO = 1, P1.7/MDY is in the HIGH state.
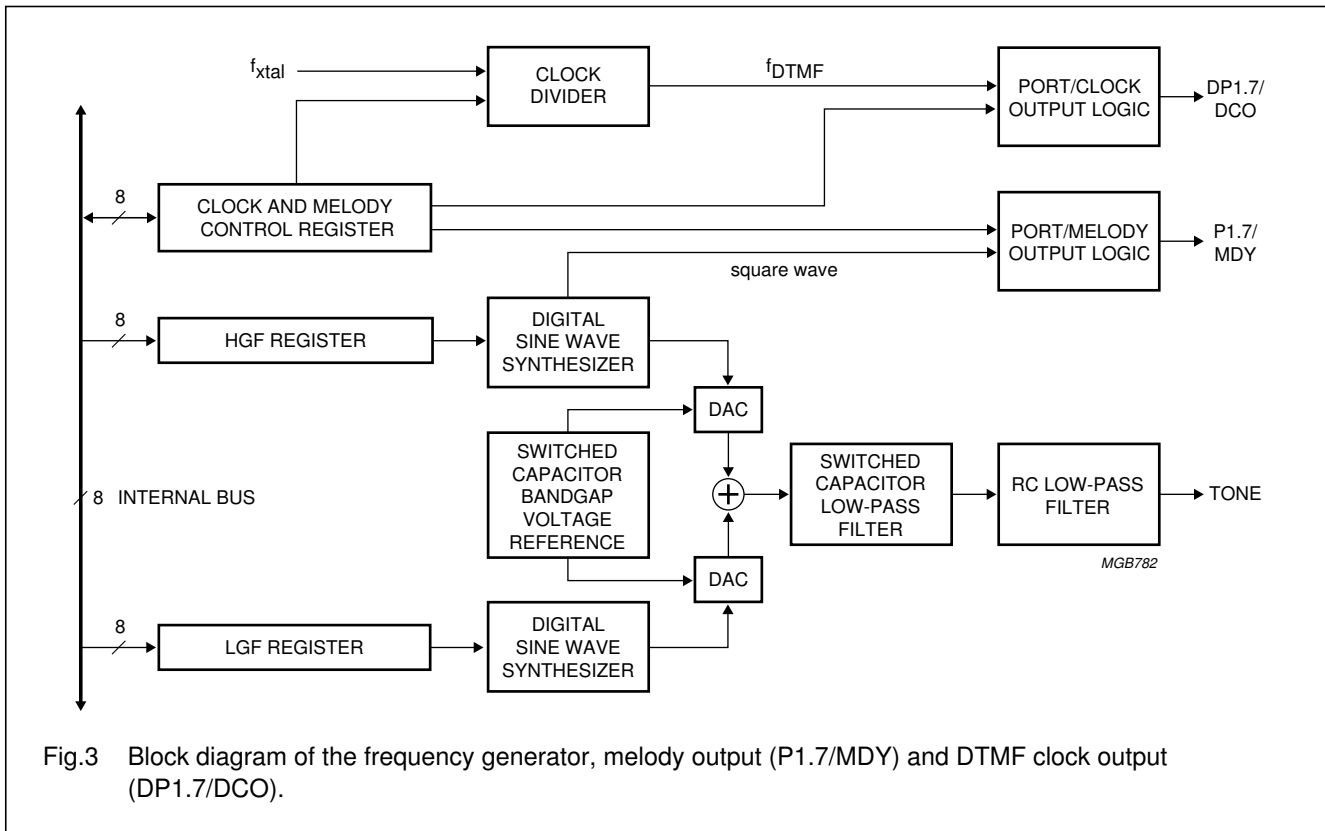
Fig.3 Block diagram of the frequency generator, melody output (P1.7/MDY) and DTMF clock output (DP1.7/DCO).

6.2 Melody output (P1.7/MDY)

The melody output (P1.7/MDY) is very useful for generating musical notes when a purely sinusoidal signal is not required, such as for ringer applications.

The square wave (duty cycle = $^{12}/_{23}$ or 52%) will include the attenuated harmonics of the base frequency, which is defined by the contents of the HGF register (Table 2). However, even higher frequency notes may be produced since the low-pass filtering on the TONE output is not applied to the P1.7/MDY output. This results in the minimum decimal value x in the HGF register (see equation in Section 6.4) being 2 for the P1.7/MDY output, rather than 60 for the TONE output. A sinusoidal TONE output is produced at the same time as the melody square wave, but due to the filtering, the higher frequency sine waves produced when x < 60 will not appear at the TONE output.

Since the melody output is shared with P1.7, the port flip-flop of P1.7 has to be set HIGH before using the melody output. This is to avoid conflicts between melody and port outputs. The melody output drive depends on the configuration of port P1.7/MDY, see Chapter 14, Table 27.

6.3 DTMF clock divider and output (DP1.7/DCO)

The DTMF clock divider allows the DTMF part to run either with the main clock frequency ($f_{DTMF} = f_{xtal}$) or with a third of it ($f_{DTMF} = \frac{1}{3} \times f_{xtal}$) depending on the state of the divider control bit DIV3 in register MDYCON.

For low power applications, a 3.58 MHz quartz crystal or PXE resonator can be chosen together with the divide-by-one function of the clock divider.

For other applications a 10.74 MHz quartz crystal or PXE resonator may be chosen together with the divide-by-three function of the clock divider. This triples the program speed of the microcontroller, thereby keeping the assumed DTMF frequency of 3.58 MHz.

Since a 3.58 MHz clock is needed for peripheral telephony circuits such as the analog voice scrambler/descrambler PCD4440T, a switchable DTMF clock output is provided depending on the state of the enable clock output bit EDCO in register MDYCON.

If EDCO = 1 and DIV3 = 1 in the MDYCON register: a square wave with the frequency $f_{DTMF} = \frac{1}{3} \times f_{xtal}$ is output on the derivative port line DP1.7/DCO. If EDCO = 1 and DIV3 = 0: a square wave with the frequency $f_{DTMF} = f_{xtal}$ is output on the derivative port line DP1.7/DCO.

The melody output drive depends on the configuration of port P1.7/MDY, see Chapter 14, Table 27.

6.4 Frequency registers

The two frequency registers HGF and LGF define two frequencies. From these, the digital sine synthesizers together with the Digital-to-Analog Converters (DACs) construct two sine waves. Their amplitudes are precisely scaled according to the bandgap voltage reference. This ensures tone output levels independent of supply voltage and temperature. The amplitude of the Low Group Frequency sine wave is attenuated by 2 dB compared to the amplitude of the High Group Frequency sine wave.

The two sine waves are summed and then filtered by an on-chip switched capacitor and RC low-pass filters. These guarantee that all DTMF tones generated fulfil the CEPT recommendations with respect to amplitude, frequency deviation, total harmonic distortion and suppression of unwanted frequency components.

The value 00H in a frequency register stops the corresponding digital sine synthesizer. If both frequency registers contain 00H, the whole frequency generator is shut off, resulting in lower power consumption.

The frequency 'f' of the sine wave generated from either of the frequency registers is a function of the clock frequency 'f_{xtal}' and the decimal value 'x' held in the register. The equation relating these variables is:

$$f = \frac{f_{xtal}}{[23\,(x+2)\,]}; \text{ where } 60 \leq x \leq 255.$$

The frequency limitation given by $x \geq 60$ is due to the low-pass filters which would attenuate higher frequency sine waves.

6.5 DTMF frequencies

Assuming an oscillator frequency $f_{xtal} = 3.58$ MHz, the DTMF standard frequencies can be implemented as shown in Table 5.

The relationships between telephone keyboard symbols, DTMF frequency pairs and the frequency register contents are given in Table 6.

Table 5 DTMF standard frequencies and their implementation; value = LGF, HGF contents

VALUE (HEX)	FREQUENCY (Hz)		DEVIATION	
	STANDARD	GENERATED	(%)	(Hz)
DD	697	697.90	0.13	0.90
C8	770	770.46	0.06	0.46
B5	852	850.45	−0.18	−1.55
A3	941	943.23	0.24	2.23
7F	1209	1206.45	−0.21	−2.55
72	1336	1341.66	0.42	5.66
67	1477	1482.21	0.35	5.21
5D	1633	1638.24	0.32	5.24

Table 6 Dialling symbols, corresponding DTMF frequency pairs and frequency register contents

TELEPHONE KEYBOARD SYMBOLS	DTMF FREQ. PAIRS (Hz)	LGF VALUE (HEX)	HGF VALUE (HEX)
0	(941, 1336)	A3	72
1	(697, 1209)	DD	7F
2	(697, 1336)	DD	72
3	(697, 1477)	DD	67
4	(770, 1209)	C8	7F
5	(770, 1336)	C8	72
6	(770, 1477)	C8	67
7	(852, 1209)	B5	7F
8	(852, 1336)	B5	72
9	(852, 1477)	B5	67
A	(697, 1633)	DD	5D
B	(770, 1633)	C8	5D
C	(852, 1633)	B5	5D
D	(941, 1633)	A3	5D
•	(941, 1209)	A3	7F
#	(941, 1477)	A3	67

6.6 Modem frequencies

Again assuming an oscillator frequency f_{xtal} = 3.58 MHz, the standard modem frequencies can be implemented as in Table 7. It is suggested to define the frequency by the HGF register while the LGF register contains 00H, disabling Low Group Frequency generation.

Table 7 Standard modem frequencies and their implementation

HGF VALUE (HEX)	FREQUENCY (Hz)		DEVIATION	
	MODEM	GENERATED	(%)	(Hz)
9D	980[1]	978.82	−0.12	−1.18
82	1180[1]	1179.03	−0.08	−0.97
8F	1070[2]	1073.33	0.31	3.33
79	1270[2]	1265.30	−0.37	−4.70
80	1200[3]	1197.17	−0.24	−2.83
45	2200[3]	2192.01	−0.36	−7.99
76	1300[4]	1296.94	−0.24	−3.06
48	2100[4]	2103.14	0.15	3.14
5C	1650[1]	1655.66	0.34	5.66
52	1850[1]	1852.77	0.15	2.77
4B	2025[2]	2021.20	−0.19	−3.80
44	2225[2]	2223.32	−0.08	−1.68

Notes

1. Standard is V.21.
2. Standard is Bell 103.
3. Standard is Bell 202.
4. Standard is V.23.

6.7 Musical scale frequencies

Finally, two octaves of musical scale in steps of semitones can be realized, again assuming an oscillator frequency f_{xtal} = 3.58 MHz (Table 8). It is suggested to define the frequency by the HGF register while the LGF contains 00H, disabling Low Group Frequency generation.

Table 8 Musical scale frequencies and their implementation

NOTE	HGF VALUE (HEX)	FREQUENCY (Hz)	
		STANDARD[1]	GENERATED
D#5	F8	622.3	622.5
E5	EA	659.3	659.5
F5	DD	698.5	697.9
F#5	D0	740.0	741.1
G5	C5	784.0	782.1
G#5	B9	830.6	832.3
A5	AF	880.0	879.3
A#5	A5	923.3	931.9
B5	9C	987.8	985.0
C6	93	1046.5	1044.5
C#6	8A	1108.7	1111.7
D6	82	1174.7	1179.0
D#6	7B	1244.5	1245.1
E6	74	1318.5	1318.9
F6	6D	1396.9	1402.1
F#6	67	1480.0	1482.2
G6	61	1568.0	1572.0
G#6	5C	1661.2	1655.7
A6	56	1760.0	1768.5
A#6	51	1864.7	1875.1
B6	4D	1975.5	1970.0
C7	48	2093.0	2103.3
C#7	44	2217.5	2223.3
D7	40	2349.3	2358.1
D#7	3D	2489.0	2470.4

Note

1. Standard scale based on A4 @ 440 Hz.

7 EEPROM AND TIMER 2 ORGANIZATION

The PCD3350A has 256 bytes of Electrically Erasable Programmable Read Only Memory (EEPROM). Such non-volatile storage provides data retention without the need for battery backup. In telecom applications, the EEPROM is used for storing redial numbers and for short dialling of frequently used numbers. More generally, EEPROM may be used for customizing microcontrollers, such as to include a PIN code or a country code, to define trimming parameters, to select application features from the range stored in ROM.

The most significant difference between a RAM and an EEPROM is that a bit in EEPROM, once written to a logic 1, cannot be cleared by a subsequent write operation. Successive write accesses actually perform a logical OR with the previously stored information. Therefore, to clear a bit, the whole byte must be erased and re-written with the particular bit cleared. Thus, an erase-and-write operation is the EEPROM equivalent of a RAM write operation.

Whereas read access times to an EEPROM are comparable to RAM access times, write and erase access times are much slower at 5 ms each. To make these operations more efficient, several provisions are available in the PCD3350A.

First, the EEPROM array is structured into 64 four-byte pages (see Fig.4) permitting access to 4 bytes in parallel (write page, erase/write page and erase page). It is also possible to erase and write individual bytes.

Finally, the EEPROM address register provides auto-incrementing, allowing very efficient read and write accesses to sequential bytes.

To simplify the erase and write timing, the derivative 8-bit down-counter (Timer 2) with reload register is provided. In addition to EEPROM timing, Timer 2 can be used for general real-time tasks, such as for measuring signal duration and for defining pulse widths.
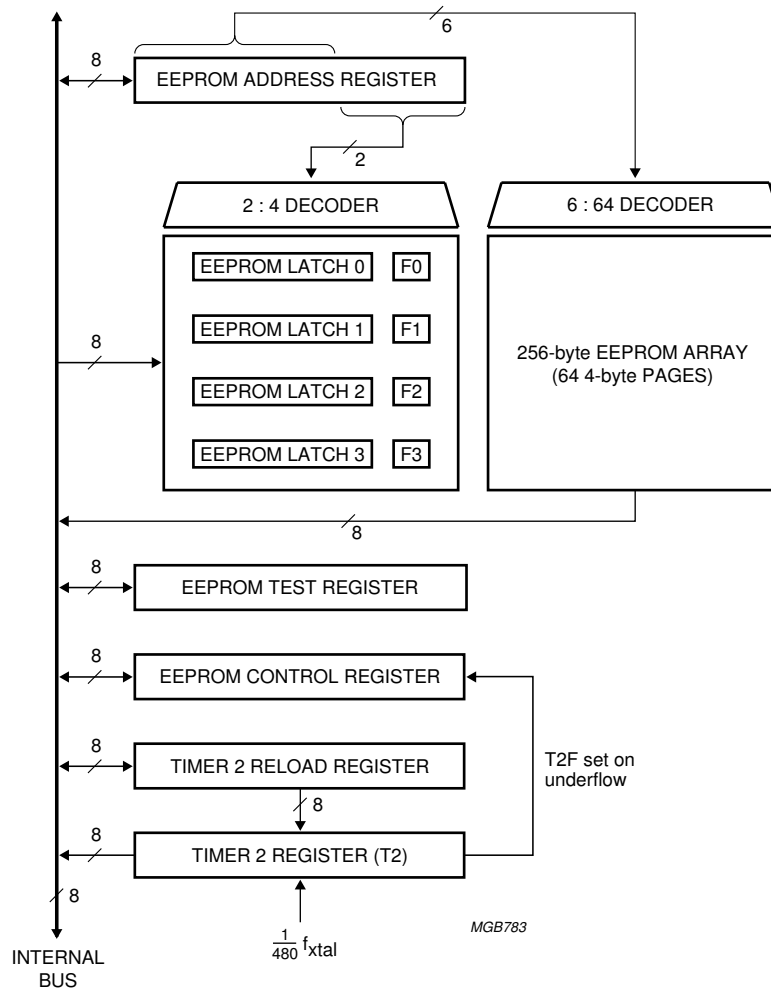
Fig.4 Block diagram of the EEPROM and Timer 2.

7.1 EEPROM registers

7.1.1 EEPROM CONTROL REGISTER (EPCR)

The behaviour of the EEPROM and Timer 2 section is defined by the EEPROM Control Register, as detailed in Tables 9, 10 and 11.

Table 9 EEPROM Control Register, EPCR (address 04H, access type R/W)

7	6	5	4	3	2	1	0
STT2	ET2I	T2F	EWP	MC3	MC2	MC1	0

Table 10 Description of EPCR bits

BIT	SYMBOL	DESCRIPTION
7	STT2	Start T2. If STT2 = 0, then Timer 2 is stopped; T2 value held. If STT2 = 1, then T2 decrements from reload value.
6	ET2I	Enable T2 interrupt. If ET2I = 0, then T2F event cannot request interrupt. If ET2I = 1, then T2F event can request interrupt.
5	T2F	Timer 2 flag. Set when T2 underflows (or by program); reset by program.
4	EWP	Erase or write in progress (EWP). Set by program (EWP starts EEPROM erase and/or write and Timer 2). Reset at the end of EEPROM erase and/or write.
3	MC3	Mode control 3 to 1. These three bits in conjunction with bit EWP select the mode as shown in Table 11.
2	MC2	
1	MC1	
0	–	This bit is set to a logic 0.

Table 11 Mode selection; X = don't care

EWP	MC3	MC2	MC1	DESCRIPTION
0	0	0	0	read byte
0	0	1	0	increment mode
1	0	1	X	write page
1	1	0	0	erase/write page
1	1	1	1	erase page
X	0	0	1	not allowed
X	1	0	1	
X	1	1	0	

7.1.2 EEPROM ADDRESS REGISTER (ADDR)

The EEPROM Address Register (ADDR) determines the EEPROM location to which an EEPROM access is directed.

As a whole, ADDR auto-increments after read and write cycles to EEPROM, but remains fixed after erase cycles. This behaviour generates the correct ADDR contents for sequential read accesses and for sequential write or erase/write accesses with intermediate page setup. Overflow of the 8-bit counter wraps around to zero. See Tables 12 and 13.

Table 12 EEPROM Address Register, ADDR (address 01H, access type R/W)

7	6	5	4	3	2	1	0
AD7	AD6	AD5	AD4	AD3	AD2	AD1	AD0

Table 13 Description of ADDR bits

BIT	SYMBOL	DESCRIPTION
7 to 2	AD7 to AD2	AD7 to AD2 select one of 64 pages.
1 to 0	AD1 to AD0	AD1 and AD0 are irrelevant during erase and write cycles. For read accesses, AD0 and AD1 indicate the byte location within an EEPROM page. During page setup, finally, AD0 and AD1 select EEPROM Latch 0 to 3 whereas AD2 to AD6 are irrelevant. If increment mode (see Table 11) is active during page setup, the subcounter consisting of AD0 and AD1 increments after every write to an EEPROM latch, thus enhancing access to sequential EEPROM latches. Incrementing stops when EEPROM Latch 3 is reached, i.e. when AD0 and AD1 are both a logic 1.

7.1.3 EEPROM DATA REGISTER (DATR)

Table 14 EEPROM Data Register, DATR (address 03H; access type R/W)

7	6	5	4	3	2	1	0
D7	D6	D5	D4	D3	D2	D1	D0

Table 15 Description of DATR bits

BIT	SYMBOL	DESCRIPTION
7 to 0	D7 to D0	The EEPROM Data Register (DATR) is only a conceptual entity. A read operation from DATR, reads out the EEPROM byte addressed by ADDR. On the other hand, a write operation to DATR, loads data into the EEPROM latch (see Fig.4) defined by bits AD0 and AD1 of ADDR.

7.1.4 EEPROM TEST REGISTER (TST)

The EEPROM Test Register is used for testing purposes during device manufacture. It must not be accessed by the device user.

7.2 EEPROM latches

The four EEPROM latches (EEPROM Latch 0 to 3; Fig.4) cannot be read by user software. Due to their construction, the latches can only be preset, but not cleared. Successive write operations through DATR to the EEPROM latches actually perform a logical OR with the previously stored data in EEPROM. The EEPROM latches are reset at the conclusion of any EEPROM cycle.

7.3 EEPROM flags

The four EEPROM flags (F0 to F3; Fig.4) cannot be directly accessed by user software. An EEPROM flag is set as a side-effect when the corresponding EEPROM latch is written through DATR. The EEPROM flags are reset at the conclusion of any EEPROM cycle.

7.4 EEPROM macros

The instruction sequence used in an EEPROM access should be treated as an indivisible entity. Erroneous programs result if ADDR, DATR, RELR or EPCR are inadvertently changed during an EEPROM cycle or its setup. Special care should be taken if the program may asynchronously divert due to an interrupt. A new access to the EEPROM may only be initiated when no write, erase or erase/write cycles are in progress. This can be verified by reading bit EWP (register EPCR).

For write, erase and erase/write cycles, it is assumed that the Timer 2 Reload Register (RELR) has been loaded with the appropriate value for a 5 ms delay, which depends on f_{xtal} (see Table 22). The end of a write, erase or erase/write cycle will be signalled by a cleared EWP and by a Timer 2 interrupt provided that ET2I = 1 and that the derivative interrupt is enabled.

7.5 EEPROM access

One read, one write, one erase/write and one erase access are defined by bits EWP and MC1 to MC3 in the EPCR register; see Table 9.

Read byte retrieves the EEPROM byte addressed by ADDR when DATR is read. Read cycles are instantaneous.

Write and erase cycles take 5 ms, however. Erase/write is a combination of an erase and a subsequent write cycle, consequently taking 10 ms.

As their names imply, **write page, erase page and erase/write page** are applied to a whole EEPROM page. Therefore, bits AD0 and AD1 of register ADDR (see Table 12), defining the byte location within an EEPROM

page, are irrelevant during write and erase cycles. However, write and erase cycles need not affect all bytes of the page. The EEPROM flags F0 to F3 (see Fig.4) determine which bytes within the EEPROM page are affected by the erase and/or write cycles. A byte whose corresponding EEPROM flag is zero remains unchanged.

With erase page, a byte is erased if its corresponding EEPROM flag is set. With write page, data in EEPROM Latch 0 to 3 (Fig.4) are ORed to the individual page bytes if and only if the corresponding EEPROM flags are set.

In an erase/write cycle, F0 to F3 select which page bytes are erased and ORed with the corresponding EEPROM latches. ORing, in this case, means that the EEPROM latches are copied to the selected page bytes.

The described page-wise organization of erase and write cycles allows up to four bytes to be individually erased or written within 5 ms. This advantage necessitates a preparation step, called **page setup**, before the actual erase and/or write cycle can be executed.

Page setup controls EEPROM latches and EEPROM flags. This will be described in the Sections 7.5.1 to 7.5.5.

7.5.1 PAGE SETUP

Page setup is a preparation step required before write page, erase page and erase/write page cycles.
As previously described, these page operations include single-byte write, erase and erase/write as a special case. EEPROM flags F0 to F3 determine which page bytes will be affected by the mentioned page operations. EEPROM Latch 0 to 3 must be preset through DATR to specify the write cycle data to EEPROM and to set the EEPROM flags as a side-effect.

Obviously, the actual preset value of the EEPROM latches is irrelevant for erase page. Preset of one, two, three or all four EEPROM latches and the corresponding EEPROM flags can be performed by repeatedly defining ADDR and writing to DATR (see Table 16).

If more than one EEPROM latch must be preset, the subcounter consisting of AD0 and AD1 can be induced to auto-increment after every write to DATR, thus stepping through all EEPROM latches. For this purpose, increment mode (Table 11) must be selected. Auto-incrementing stops at EEPROM Latch 3. It is not mandatory to start at EEPROM Latch 0 as in shown in Table 17.

Note that AD2 to AD7 are irrelevant during page setup. They will usually specify the intended EEPROM page, anticipating the subsequent page cycle.

From now on, it will be assumed that AD2 to AD7 will contain the intended EEPROM page address after page setup.

Table 16 Page setup; preset

INSTRUCTION	RESULT
MOV A, #addr	address of EEPROM latch
MOV ADDR, A	send address to ADDR
MOV A, #data	load write, erase/write or erase data
MOV DATR, A	send data to addressed EEPROM latch

Table 17 Page setup; auto-incrementing

INSTRUCTION	RESULT
MOV A, #MC2	increment mode control word
MOV EPCR, A	select increment mode
MOV A, #baddr	EEPROM Latch 0 address (AD0 = AD1 = 0)
MOV ADDR, A	send EEPROM Latch 0 address to ADDR
MOV A, R0	load 1st byte from Register 0
MOV DATR, A	send 1st byte to EEPROM Latch 0
MOV A, R1	load 2nd byte from Register 1
MOV DATR, A	send 2nd byte to EEPROM Latch 1
MOV A, R2	load 3rd byte from Register 2
MOV DATR, A	send 3rd byte to EEPROM Latch 2
MOV A, R3	load 4th byte from Register 3
MOV DATR, A	send 4th byte to EEPROM Latch 3

7.5.2 READ BYTE

Since ADDR auto-increments after a read cycle regardless of the page boundary, successive bytes can efficiently be read by repeating the last instruction.

Table 18 Read byte

INSTRUCTION	RESULT
MOV A, #RDADDR	load read address
MOV ADDR, A	send address to ADDR
MOV A, DATR	read EEPROM data

7.5.3 WRITE PAGE

The write cycle performs a logical OR between the data in the EEPROM latches and that in the addressed EEPROM page. To actually copy the data from the EEPROM latches, the corresponding bytes in the page should previously have been erased.

The EEPROM latches are preset as described in Section 7.5.1. The actual transfer to the EEPROM is then performed as shown in Table 19.

The last instruction also starts Timer 2. The data in the EEPROM latches are ORed with that in the corresponding page bytes within 5 ms. A single-byte write is simply a special case of 'write page'.

ADDR auto-increments after the write cycle. If AD0 and AD1 addressed EEPROM Latch 3 prior to the write cycle, ADDR will point to the next EEPROM page (by bits AD2 to AD7) and to EEPROM Latch 0 (by bits AD0 and AD1). This allows efficient coding of multi-page write operations.

Table 19 Write page

INSTRUCTION	RESULT
MOV A, #EWP + MC2	'write page' control word
MOV EPCR, A	start 'write page' cycle

7.5.4 ERASE/WRITE PAGE

The EEPROM latches are preset as described in Section 7.5.1. The page bytes corresponding to the asserted flags (among F0 to F3) are erased and re-written with the contents of the respective EEPROM latches.

The last instruction also starts Timer 2. Erasure takes 5 ms upon which Timer Register T2 reloads for another 5 ms cycle for writing. The top cycles together take 10 ms. A single-byte erase/write is simply a special case of 'erase/write page'.

ADDR auto-increments after the write cycle. If AD0 and AD1 addressed EEPROM Latch 3 prior to the write cycle, ADDR will point to the next EEPROM page (by AD2 to AD7) and to EEPROM Latch 0 (by AD0 and AD1). This allows efficient coding of multi-page erase/write operations.

Table 20 Erase/write page

INSTRUCTION	RESULT
MOV A, #EWP + MC3	'erase/write page' control word
MOV EPCR, A	start 'erase/write page' cycle

7.5.5 ERASE PAGE

The EEPROM flags are set as described in Section 7.5.1.
The corresponding page bytes are erased.

The last instruction also starts Timer 2. Erasure takes
5 ms. A single-byte erase is simply a special case of
'erase page'.

Note that ADDR does not auto-increment after an erase
cycle.

Table 21 Erase page

INSTRUCTION	RESULT
MOV A, #EWP + MC3 + MC2 + MC1	'erase page' control word
MOV EPCR, A	start 'erase page' cycle

7.6 Timer 2

Timer 2 is a 8-bit down-counter decremented at a rate of
$\frac{1}{480} \times f_{xtal}$. It may be used either for EEPROM timing or as
a general purpose timer. Conflicts between the two
applications should be carefully avoided.

7.6.1 TIMER 2 FOR EEPROM TIMING

When used for EEPROM timing, Timer 2 serves to
generate the 5 ms intervals needed for erasing or writing
the EEPROM. At the decrement rate of $\frac{1}{480} \times f_{xtal}$, the
reload value for a 5 ms interval is a function of f_{xtal}.
Table 22 summarizes the required reload values for a
number of oscillator frequencies.

Timer 2 is started by setting bit EWP in the EPCR.
The Timer Register T2 is loaded with the reload value from
RELR. T2 decrements to zero.

For an erase/write cycle, underflow of T2 indicates the end
of the erase operation. Therefore, Timer Register T2 is
reloaded from RELR for another 5 ms interval during
which the flagged EEPROM latches are copied to the
corresponding bytes in the page addressed by ADDR.

The second underflow of an erase/write cycle and the first
underflow of write page and erase page conclude the
corresponding EEPROM cycle. Timer 2 is stopped, T2F is
set whereas EWP and MC1 to MC3 are cleared.

Table 22 Reload values as a function of f_{xtal}

f_{xtal} (MHz)	RELOAD VALUE[1] (HEX)
1	0A
2	14
3.58	25
6	3E
10.74	6F
16	A6

Note

1. The reload value is $(5 \times 10^{-3} \times \frac{1}{480} \times f_{xtal}) - 1$;
   f_{xtal} in MHz.

7.6.2 TIMER 2 AS A GENERAL PURPOSE TIMER

When used for purposes other than EEPROM timing,
Timer 2 is started by setting STT2. The Timer 2 Register
T2 (see Table 28) is loaded with the reload value from
RELR. T2 decrements to zero. On underflow, T2 is
reloaded from RELR, T2F is set and T2 continues to
decrement.

Timer 2 can be stopped at any time by clearing STT2.
The value of T2 is then held and can be read out. After
setting STT2 again, Timer 2 decrements from the reload
value. Alternatively, it is possible to read T2 'on the fly' i.e.
while Timer 2 is operating.

8   REAL-TIME CLOCK

The Real Time Clock (RTC) consists of a 32 kHz crystal oscillator, a 32 kHz to 1 second or 1 minute divider chain, an 8-bit Frequency Adjustment Register and the Clock Control Register. The complete RTC section works independently of the microcontroller status, even in Idle and Stop mode.

8.1   Oscillator

The internal 32 kHz oscillator needs an external quartz crystal with a frequency of 32768.00 Hz (a positive deviation up to $+259 \times 10^{-6}$ is allowed) and an external feedback resistor between pins RTC1 and RTC2; 4.7 MΩ is recommended. It is controlled by the RUN-bit in the Clock Control Register.

8.2   Divider chain

The divider chain operates with the 32 kHz oscillator output and divides this signal down to two clocks with a period of 1 second or 1 minute. Depending on bit ITS in the Clock Control Register, the falling edge of the seconds or minutes clock is used to set the Clock Interrupt Flag (CIF) in the Clock Control Register.

Since the clock interrupt is used to let the microcontroller leave the Stop mode, it is ORed to the external interrupt (CE/$\overline{T0}$) and has the same functionality, e.g. it must be enabled in the Clock Control Register (bit ECI) and by execution of the instruction 'EN I'. The clock interrupt will then be treated as an external interrupt.

Additionally, the divider chain generates a 16 kHz clock (RCO) that can be routed through derivative port line DP0.0/RCO, controlled by bit ERCO in the Clock Control Register.

8.3   Frequency adjustment

The frequency adjustment is used to extend the interrupt time by defining the number of 16 kHz clocks in the Frequency Adjustment Register that will be counted twice within the first second period after a minute interrupt.

If the second interrupt is used (ITS = 1), every 60th interval may be up to 15.3 ms longer than the others as a result of the frequency adjustment. The adjusted Minute Interrupt Time (MIT) now shows a maximum deviation of 0.5×10^{-6}.

8-bit microcontroller with DTMF generator,
256 bytes EEPROM and real-time clock

PCD3350A

8.4 Real-time clock derivative registers

8.4.1 CLOCK CONTROL REGISTER (CLCR)

The register access type is R/W and the value at reset is 00H.

Table 23 Clock Control Register, CLCR (address 20H)

7	6	5	4	3	2	1	0
0	TST2	TST1	ERCO	RUN	ITS	CIF	ECI

Table 24 Description of CLCR bits

BIT	SYMBOL	DESCRIPTION
7	–	This bit is set to a logic 0.
6	TST2	Test 2 input. This is a testing bit; has to be fixed at a logic 0 by user software.
5	TST1	Test 1 input. This is a testing bit; has to be fixed at a logic 0 by user software.
4	ERCO	Enable 16 kHz clock output. If ERCO = 0, then the DP0.0/RCO is a derivative port line. If ERCO = 1, then DP0.0./RCO is a 16 kHz clock output. ERCO = 1 does not inhibit the port instructions for DP0.0/RCO. Therefore the state of both port line and flip-flop may be read in and the port flip-flop may be written by derivative port instructions. However, the port flip-flop of DP0.0/RCO must remain set to avoid conflicts between 16 kHz clock and port outputs.
3	RUN	Clock run or stop bit. If RUN = 0, then the oscillator is stopped and the clock is reset. If RUN = 1, then the oscillator and the clock are running.
2	ITS	Interrupt Time Select. If ITS = 1, then the interrupt time is one second. If ITS = 0, then the interrupt time is one minute.
1	CIF	Clock Interrupt Flag. Set by hardware, if RTC divider chain overflows (every second or minute depending on ITS) or by program. Reset by program.
0	ECI	Enable Clock Interrupt. If ECI = 0, then CIF event cannot request interrupt. If ECI = 1, then CIF event requests interrupt.

8.4.2 FREQUENCY ADJUSTMENT REGISTER (FAR)

The frequency adjustment value of the RTC is defined by the 8-bit Frequency Adjustment Register. The register access type is R/W. The value of FAR at reset is 00H.

The significance of the individual bits of FAR can be illustrated by the following equation:

$$\text{Minute Interrupt Time (MIT)} = \left(60 \times 2^{\frac{14}{f_{RCO}}} \right) + \frac{FAR}{2^{14}}$$

where f_{RCO} = RTC frequency and 'FAR' is the decimal contents of the Frequency Adjustment Register.

Table 26 shows the recommended correction factor FAR for all allowed RTC frequencies f_{RCO}.

Table 25 Frequency Adjustment Register, FAR (address 21H)

7	6	5	4	3	2	1	0
FAR7	FAR6	FAR5	FAR4	FAR3	FAR2	FAR1	FAR0

8-bit microcontroller with DTMF generator,
256 bytes EEPROM and real-time clock

PCD3350A

Table 26 FAR as a result of f_{RCO}

f_{RCO}	FAR (HEX)	f_{RCO}	FAR (HEX)	f_{RCO}	FAR (HEX)
16384.000	00	16384.500	1E	16385.018	3D
16384.018	01	16384.518	1F	16385.033	3E
16384.033	02	16384.533	20	16385.051	3F
16384.051	03	16384.551	21	16385.066	40
16384.066	04	16384.566	22	16385.084	41
16384.084	05	16384.584	23	16385.100	42
16384.100	06	16384.600	24	16385.117	43
16384.117	07	16384.617	25	16385.135	44
16384.135	08	16384.635	26	16385.150	45
16384.150	09	16384.650	27	16385.168	46
16384.168	0A	16384.668	28	16385.184	47
16384.184	0B	16384.684	29	16385.201	48
16384.201	0C	16384.701	2A	16385.217	49
16384.217	0D	16384.717	2B	16385.234	4A
16384.234	0E	16384.734	2C	16385.250	4B
16384.250	0F	16384.750	2D	16385.268	4C
16384.268	10	16384.768	2E	16385.283	4D
16384.283	11	16384.783	2F	16385.301	4E
16384.301	12	16384.801	30	16385.316	4F
16384.316	13	16384.816	31	16385.334	50
16384.334	14	16384.834	32	16385.350	51
16384.350	15	16384.850	33	16385.367	52
16384.367	16	16384.867	34	16385.385	53
16384.385	17	16384.885	35	16385.400	54
16384.400	18	16384.900	36	16385.418	55
16384.418	19	16384.918	37	16385.434	56
16384.434	1A	16384.934	38	16385.451	57
16384.451	1B	16384.951	39	16385.467	58
16384.467	1C	16384.967	3A	16385.484	59
16384.484	1D	16384.984	3B	16385.500	5A
		16385.000	3C	16385.518	5B

f_{RCO}	FAR (HEX)	f_{RCO}	FAR (HEX)	f_{RCO}	FAR (HEX)
16385.533	5C	16386.000	78	16386.467	94
16385.551	5D	16386.018	79	16386.484	95
16385.566	5E	16386.033	7A	16386.500	96
16385.584	5F	16386.051	7B	16386.518	97
16385.600	60	16386.066	7C	16386.533	98
16385.617	61	16386.084	7D	16386.551	99
16385.635	62	16386.100	7E	16386.566	9A
16385.650	63	16386.117	7F	16386.584	9B
16385.668	64	16386.135	80	16386.600	9C
16385.684	65	16386.150	81	16386.617	9D
16385.701	66	16386.168	82	16386.635	9E
16385.717	67	16386.184	83	16386.650	9F
16385.734	68	16386.201	84	16386.668	A0
16385.750	69	16386.217	85	16386.684	A1
16385.768	6A	16386.234	86	16386.701	A2
16385.783	6B	16386.250	87	16386.717	A3
16385.801	6C	16386.268	88	16386.734	A4
16385.816	6D	16386.283	89	16386.750	A5
16385.834	6E	16386.301	8A	16386.768	A6
16385.850	6F	16386.316	8B	16386.783	A7
16385.867	70	16386.334	8C	16386.801	A8
16385.885	71	16386.350	8D	16386.816	A9
16385.900	72	16386.367	8E	16386.834	AA
16385.918	73	16386.385	8F	16386.850	AB
16385.934	74	16386.400	90	16386.867	AC
16385.951	75	16386.418	91	16386.885	AD
16385.967	76	16386.434	92	16386.900	AE
16385.984	77	16386.451	93	16386.918	AF

f_{RCO}	FAR (HEX)	f_{RCO}	FAR (HEX)	f_{RCO}	FAR (HEX)
16386.934	B0	16387.385	CB	16387.834	E6
16386.951	B1	16387.400	CC	16387.850	E7
16386.967	B2	16387.418	CD	16387.867	E8
16386.984	B3	16387.434	CE	16387.885	E9
16387.000	B4	16387.451	CF	16387.900	EA
16387.018	B5	16387.467	D0	16387.918	EB
16387.033	B6	16387.484	D1	16387.934	EC
16387.051	B7	16387.500	D2	16387.951	ED
16387.066	B8	16387.518	D3	16387.967	EE
16387.084	B9	16387.533	D4	16387.984	EF
16387.100	BA	16387.551	D5	16388.002	F0
16387.117	BB	16387.566	D6	16388.018	F1
16387.135	BC	16387.584	D7	16388.035	F2
16387.150	BD	16387.600	D8	16388.051	F3
16387.168	BE	16387.617	D9	16388.068	F4
16387.184	BF	16387.635	DA	16388.084	F5
16387.201	C0	16387.650	DB	16388.102	F6
16387.217	C1	16387.668	DC	16388.117	F7
16387.234	C2	16387.684	DD	16388.135	F8
16387.250	C3	16387.701	DE	16388.152	F9
16387.268	C4	16387.717	DF	16388.168	FA
16387.283	C5	16387.734	E0	16388.186	FB
16387.301	C6	16387.750	E1	16388.201	FC
16387.316	C7	16387.768	E2	16388.219	FD
16387.334	C8	16387.783	E3	16388.234	FE
16387.350	C9	16387.801	E4	16384.000	FF
16387.367	CA	16387.816	E5		

9 DERIVATIVE INTERRUPTS

One derivative interrupt event is defined. It is controlled by
bits T2F and ET2I in the EPCR (see Tables 9 and 10).

The derivative interrupt event occurs when T2F is set. This
request is honoured under the following circumstances:

• No interrupt routine proceeds

• No external interrupt request is pending

• The derivative interrupt is enabled

• ET2I is set.

The derivative interrupt routine must include instructions
that will remove the cause of the derivative interrupt by
explicitly clearing T2F. If the derivative interrupt is not
used, T2F may directly be tested by the program.
Obviously, T2F can also be asserted under program
control, e.g. to generate a software interrupt.

Although the clock interrupt is part of a derivative function
it is linked to the external interrupt. A clock interrupt
request is honoured under the following circumstances:

• No interrupt routine proceeds

• No external interrupt request is pending

• The enable clock interrupt bit in the derivative clock
control register is set.

10 TIMING

Although the PCD3350A operates over a clock frequency
range from 1 to 16 MHz, f_{xtal} = 3.58 MHz or 10.74 MHz will
usually be chosen to take full advantage of the frequency
generator (DTMF) section.

11 RESET

In addition to the conditions given in the *"PCD33xxA
Family"* data sheet, all derivative registers are cleared in
the reset state.

12 IDLE MODE

In Idle mode all derivative functions remain operative, i.e.:

• DTMF generator

• DTMF clock divider and output

• 32 kHz crystal oscillator and RTC

• EEPROM and Timer 2 sections.

13 STOP MODE

Since the oscillator is switched off, the frequency
generator, the EEPROM and the Timer 2 sections receive
no clock. It is suggested to clear both the HGF and the
LGF registers before entering Stop mode. This will cut off
the biasing of the internal amplifiers, considerably
reducing current requirements.

The Stop mode **must not** be entered while an erase
and/or write access to EEPROM is in progress. The STOP
instruction may only be executed when EWP in EPCR is
zero. The Timer 2 section is frozen during Stop mode.
After exit from Stop mode by a HIGH level on CE/$\overline{T0}$,
Timer 2 proceeds from the held state.

The 32 kHz crystal oscillator and the RTC section remain
operative during Stop mode (depending only on bit RUN in
the Clock Control Register). In addition to the description
in the *"PCD33xxA Family"* data sheet, Stop mode may be
left by a clock interrupt event (see Chapter 9).

14 SUMMARY OF I/O PORTS AND ROM MASK OPTIONS

All standard quasi-bidirectional I/O ports are available; see *"PCD33xxA Family"* data sheet.

- Port 0: 8 parallel port lines P0.0 to P0.7
- Port 1: 8 parallel port lines P1.0 to P1.7
- Port 2: 4 parallel port lines P2.0 to P2.3.

In addition to the standard ports, two derivative I/O ports are available:

- Derivative Port 0: 6 parallel port lines DP0.0 to DP0.5 (register DP0L)
- Derivative Port 1: 8 parallel port lines DP1.0 to DP1.7 (register DP1L).

The port options and the other ROM mask options are listed in Table 27. See Table 28 for the addresses of DP0L and DP1L.

Table 27 ROM mask options

FUNCTION IMPLEMENTED IN ROM	OPTION		
Program/data	Any mix of instructions and data up to ROM size of 8 kbytes.		
Port Output			
P0.0 to P0.7	standard	open-drain	push-pull
P1.0 to P1.6	standard	open-drain	push-pull
P1.7/MDY; note 1	standard	open-drain	push-pull
P2.0 to P2.3	standard	open-drain	push-pull
DP0.0 to DP0.5	standard	open-drain	push-pull
DP1.0 to DP1.6	standard	open-drain	push-pull
DP1.7/DCO; note 2	standard	open-drain	push-pull
Port State after reset			
P0.0 to P0.7	set	reset	–
P1.0 to P1.6	set	reset	–
P1.7/MDY	set	reset	–
P2.0 to P2.3	set	reset	–
DP0.0 to DP0.5	set	reset	–
DP1.0 to DP1.6	set	reset	–
DP1.7/DCO	set	reset	–
Oscillator			
Transconductance	LOW (g_{mL})	MEDIUM (g_{mM})	HIGH (g_{mH})
Power-on-reset			
Power-on-reset voltage level: V_{POR}	1.2 to 3.6 V in increments of 100 mV; OFF		

Notes

1. If standard (Option 1) or push-pull (Option 3) output is chosen, the P1.7/MDY output becomes a push-pull output. If open-drain (Option 2) is chosen, the P1.7/MDY output becomes an open-drain output.

2. If standard (Option 1) or push-pull (Option 3) output is chosen, the DP1.7/DCO output becomes a push-pull output. If open-drain (Option 2) is chosen, the DP1.7/DCO output becomes an open-drain output.

8-bit microcontroller with DTMF generator,
256 bytes EEPROM and real-time clock

PCD3350A

15 SUMMARY OF DERIVATIVE REGISTERS

Table 28 Register map

ADDR. (HEX)	REGISTER	7	6	5	4	3	2	1	0	R/W
00	not used									
01	EEPROM Address Register (ADDR)	0	AD6	AD5	AD4	AD3	AD2	AD1	AD0	R/W
02	not used									
03	EEPROM Data Register (DATR)	D7	D6	D5	D4	D3	D2	D1	D0	R/W
04	EEPROM Control Register (EPCR)	STT2	ET21	TF2	EWP	MC3	MC2	MC1	0	R/W
05	Timer 2 Reload Register (RELR)	R7	R6	R5	R4	R3	R2	R1	R0	R/W
06	Timer 2 Register (T2)	T2.7	T2.6	T2.5	T2.4	T2.3	T2.2	T2.1	T2.0	R
07	Test Register (TST)	only for test purposes; not to be accessed by the device user								
08 to 10	not used									
11	High Group Frequency Register (HGF)	H7	H6	H5	H4	H3	H2	H1	H0	W
12	Low Group Frequency Register (LGF)	L7	L6	L5	L4	L3	L2	L1	L0	W
13	Clock and Melody Control Register (MDYCON)	0	0	0	0	0	DCO	DIV3	EMO	R/W
14 to 1F	not used									
20	Clock Control Register (CLCR)	0	TST2	TST1	ERCO	RUN	ITS	CIF	ECI	R/W
21	Frequency Adjustment Register (FAR)	FAR7	FAR6	FAR5	FAR4	FAR3	FAR2	FAR1	FAR0	R/W
22 to 2F	not used									
30	Derivative Port 0 lines (DP0L)	0	0	D0.5	D0.4	D0.3	D0.2	D0.1	D0.0	R
31	Derivative Port 1 lines (DP1L)	D1.7	D1.6	D1.5	D1.4	D1.3	D1.2	D1.1	D1.0	R
32	Derivative Port 0 flip-flop (DP0FF)	0	0	F0.5	F0.4	F0.3	F0.2	F0.1	F0.0	R/W
33	Derivative Port 1 flip-flop (DP1FF)	F1.7	F1.6	F1.5	F1.4	F1.3	F1.2	F1.1	F1.0	R/W
34 to FF	not used									

16 HANDLING

Inputs and outputs are protected against electrostatic discharge in normal handling. However, it is good practice to take normal precautions appropriate to handling MOS devices (see *"Data Handbook IC14, Section: Handling MOS devices"*).

17 LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V_{DD}	supply voltage	−0.5	+7.0	V
V_I	all input voltages	−0.5	V_{DD} + 0.5	V
I_I	DC input current	−10	+10	mA
I_O	DC output current	−10	+10	mA
P_{tot}	total power dissipation	−	125	mW
P_O	power dissipation per output	−	30	mW
I_{SS}	ground supply current	−50	+50	mA
T_{stg}	storage temperature	−65	+150	°C
T_j	operating junction temperature	−	90	°C

18 DC CHARACTERISTICS

V_{DD} = 1.8 to 6 V; V_{SS} = 0 V; T_{amb} = −25 to +70 °C; all voltages with respect to V_{SS}; f_{xtal} = 3.58 MHz (g_{mL});
f_{RTC} = 32768 to 32768 + (32768 × 200 × 10^{-6}) Hz; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Supply						
V_{DD}	supply voltage	see Fig.5				
	operating	note 1	1.8	−	6	V
	RAM data retention in Stop mode		1.0	−	6	V
I_{DD}	operating supply current	see Figs 6 and 7; note 2				
		V_{DD} = 3 V; value HGF or LGF ≠ 0	−	0.8	1.6	mA
		V_{DD} = 3 V; value HGF = LGF = 0	−	0.35	0.7	mA
		V_{DD} = 5 V; f_{xtal} = 10.74 MHz (g_{mM}); value HGF or LGF ≠ 0; DIV3 = 1	−	2.7	6.2	mA
		V_{DD} = 5 V; f_{xtal} = 10.74 MHz (g_{mM}); value HGF = LGF = 0	−	1.7	4.2	mA
		V_{DD} = 5 V; f_{xtal} = 16 MHz (g_{mH}); value HGF = LGF = 0	−	3.5	−	mA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{DD(idle)}$	supply current (Idle mode)	see Figs 8 and 9; note 2				
		V_{DD} = 3 V; value HGF or LGF ≠ 0	–	0.7	1.4	mA
		V_{DD} = 3 V; value HGF = LGF =0	–	0.25	0.5	mA
		V_{DD} = 5 V; f_{xtal} = 10.74 MHz (g_{mM}); value HGF or LGF ≠ 0; DIV3 = 1	–	2.3	5.5	mA
		V_{DD} = 5 V; f_{xtal} = 10.74 MHz (g_{mM}); value HGF = LGF = 0	–	1.3	3.5	mA
		V_{DD} = 5 V; f_{xtal} = 16 MHz (g_{mH}); value HGF = LGF = 0	–	2.4	–	mA
$I_{DD(stp)}$	supply current (Stop mode)	see Fig.10; notes 2 and 3				
		V_{DD} = 1.8 V; T_{amb} = 25 °C; RTC not running	–	1.0	5.5	μA
		V_{DD} = 1.8 V; T_{amb} = −25 to +70 °C; RTC not running	–	–	10	μA
		V_{DD} = 1.8 V; T_{amb} = 25 °C; RTC running	–	2.0	6.0	μA
Inputs						
V_{IL}	LOW level input voltage		0	–	$0.3V_{DD}$	V
V_{IH}	HIGH level input voltage		$0.7V_{DD}$	–	V_{DD}	V
I_{LI}	input leakage current	$V_{SS} ≤ V_I ≤ V_{DD}$	−1	–	+1	μA
Port outputs						
I_{OL}	LOW level output sink current	V_{DD} = 3 V; V_O = 0.4 V; see Fig.11	0.7	3.5	–	mA
I_{OH}	HIGH level pull-up output source current	V_{DD} = 3 V; V_O = 2.7 V; see Fig.12	−10	−30	–	μA
		V_{DD} = 3 V; V_O = 0 V; see Fig.12	–	−140	−300	μA
I_{OH1}	HIGH level push-pull output source current	V_{DD} = 3 V; V_O = 2.6 V; see Fig.13	−0.7	−3.5	–	mA
Real-time clock 32 kHz oscillator						
g_m	transconductance	$V_{i(p-p)}$ < 50 mV; see Fig.14	2	10	50	μS
δf/f	frequency adjustment		$-0.6 × 10^{-6}$	–	$+0.6 × 10^{-6}$	
C_i	input capacitance (pin 10)		–	10	–	pF
C_o	output capacitance (pin 11)		–	10	–	pF
TONE output (see Fig.15; notes 1 and 4)						
$V_{HG(RMS)}$	HGF voltage (RMS value)		158	181	205	mV
$V_{LG(RMS)}$	LGF voltage (RMS value)		125	142	160	mV
Δf/f	frequency deviation		−0.6	–	0.6	%
V_{DC}	DC voltage level		–	$0.5V_{DD}$	–	V
$|Z_o|$	output impedance		–	100	500	Ω
G_v	pre-emphasis of group		1.5	2.0	2.5	dB
THD	total harmonic distortion	T_{amb} = 25 °C; note 5	–	−25	–	dB

8-bit microcontroller with DTMF generator,
256 bytes EEPROM and real-time clock

PCD3350A

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
EEPROM (notes 1 and 6)						
n_{cyc}	endurance (erase/write cycles)	note 7	10^5	–	–	
$t_{D(ret)}$	data retention		10	–	–	years
Power-on-reset						
ΔV_{POR}	Power-on-reset level variation around chosen V_{POR}	note 8	–0.5	0	+0.5	V
Oscillator (see Fig. 17)						
g_{mL}	LOW transconductance	V_{DD} = 5 V	0.2	0.4	1.0	mS
g_{mM}	MEDIUM transconductance	V_{DD} = 5 V	0.9	1.6	3.2	mS
g_{mH}	HIGH transconductance	V_{DD} = 5 V	3	4.5	9.0	mS
R_F	feedback resistor		0.3	1.0	3.0	MΩ

Notes

1. TONE output; EEPROM erase and write require $V_{DD} \geq 2.5$ V:

    a) TONE output requires $f_{xtal} < 4$ MHz in case DIV3 = 0.

    b) TONE output requires $f_{xtal} < 12$ MHz in case DIV3 = 1.

2. $V_{IL} = V_{SS}$; $V_{IH} = V_{DD}$; open-drain outputs connected to V_{SS}; all other outputs open:

    a) Maximum values: external clock at XTAL1 and XTAL2 open-circuit.

    b) Typical values: T_{amb} = 25 °C; crystal connected between XTAL1 and XTAL2.

3. $V_{IL} = V_{SS}$; $V_{IH} = V_{DD}$; RESET, T1 and CE/$\overline{T0}$ at V_{SS}; crystal connected between XTAL1 and XTAL2; open-drain outputs connected to V_{SS}; all other outputs open.

4. Values are specified for DTMF frequencies only (CEPT).

5. Related to the Low Group Frequency (LGF) component (CEPT).

6. After final testing the value of each EEPROM bit is typically logic 1.

7. Verified on sampling basis.

8. V_{POR} is an option chosen by the user. Depending on its value, it may restrict the supply voltage range.
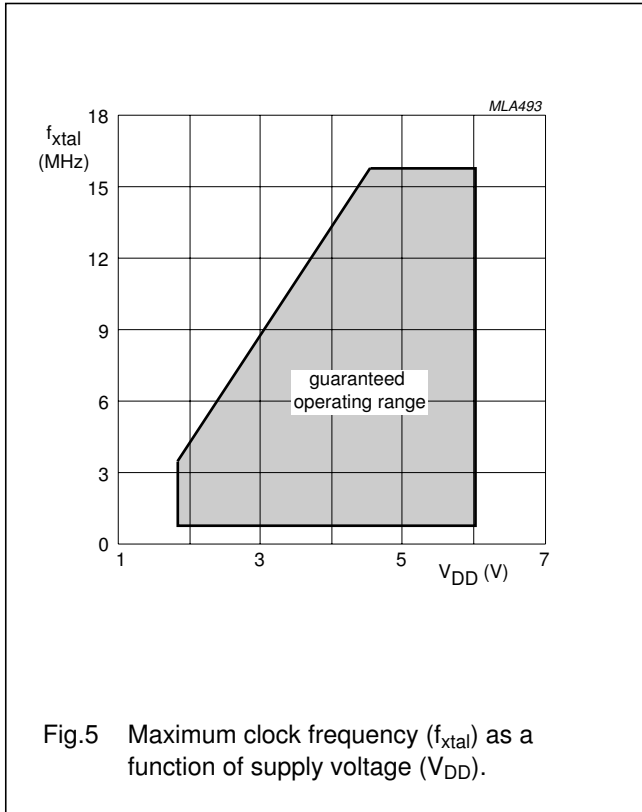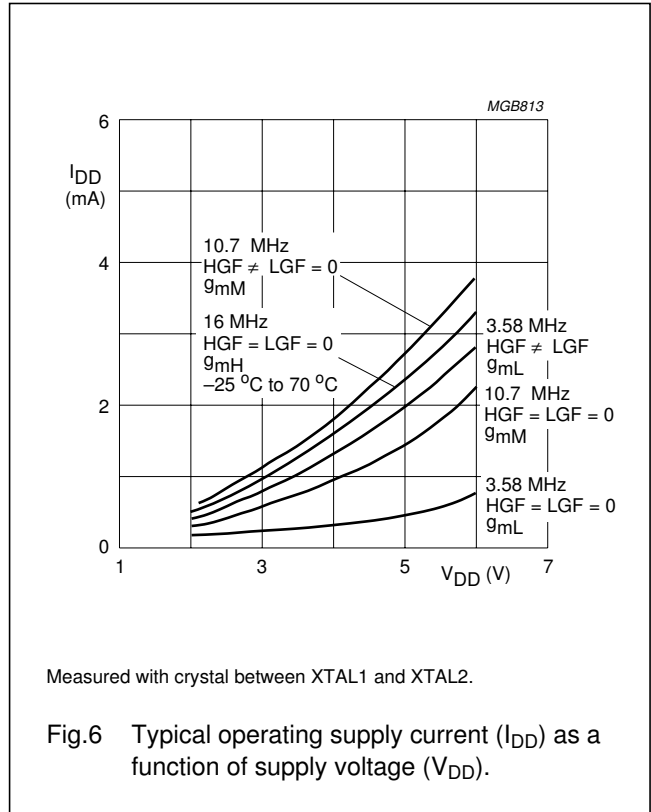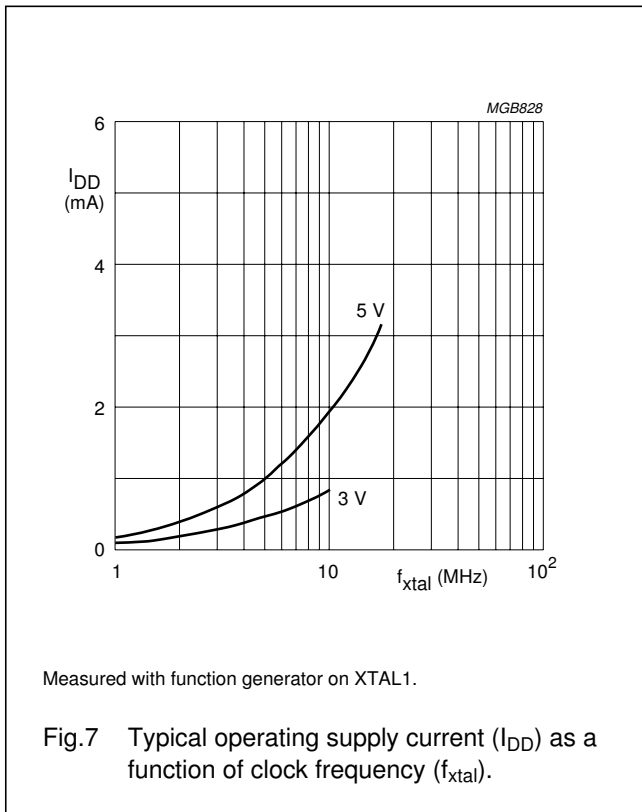
Fig.5   Maximum clock frequency (f_{xtal}) as a
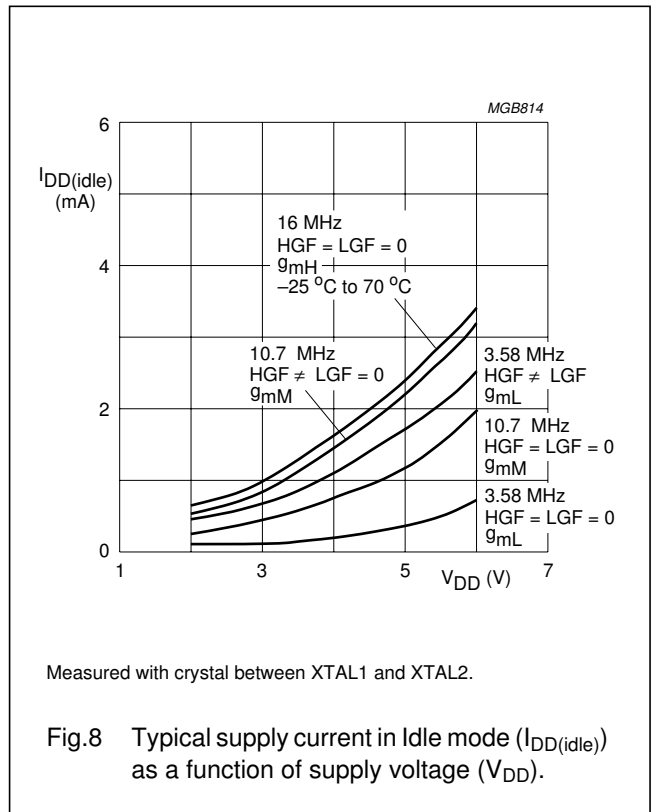function of supply voltage (V_{DD}).

Measured with crystal between XTAL1 and XTAL2.

Fig.6   Typical operating supply current (I_{DD}) as a
function of supply voltage (V_{DD}).

Measured with function generator on XTAL1.

Fig.7   Typical operating supply current (I_{DD}) as a
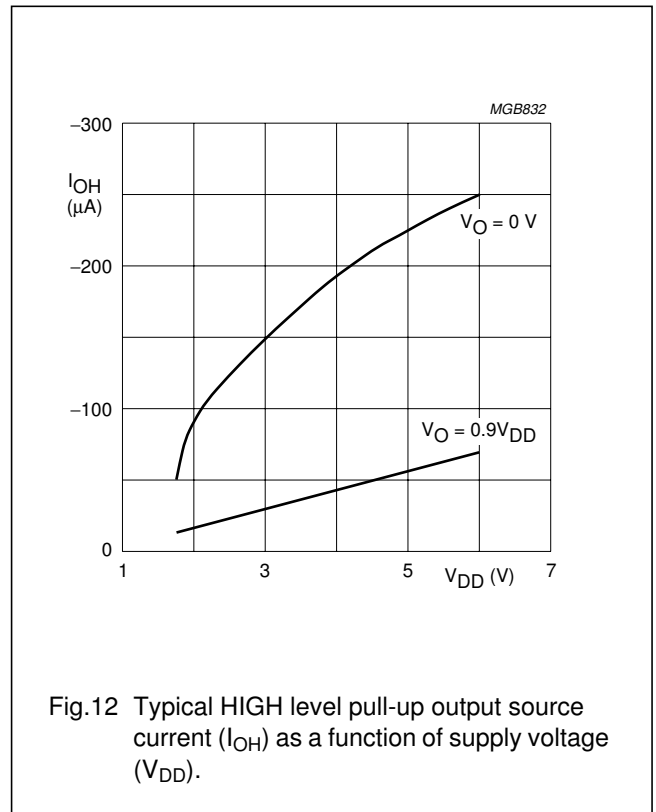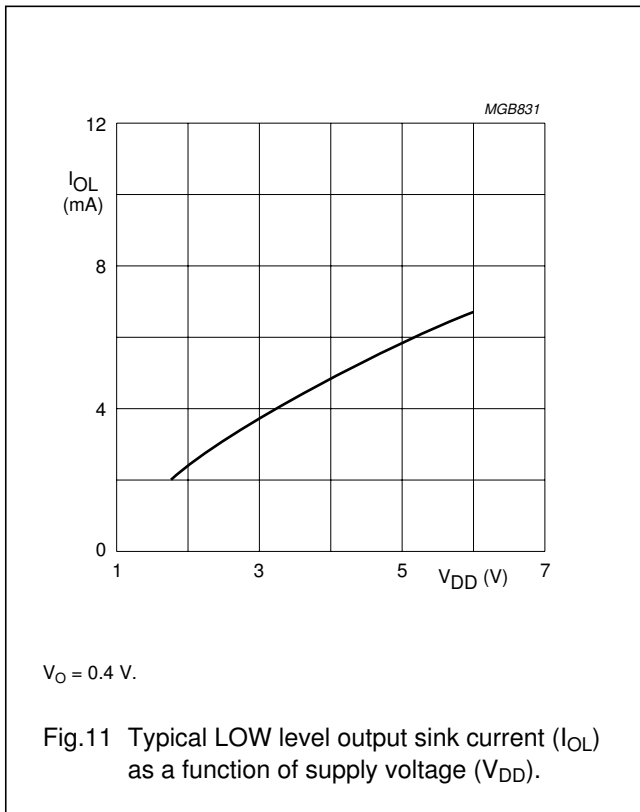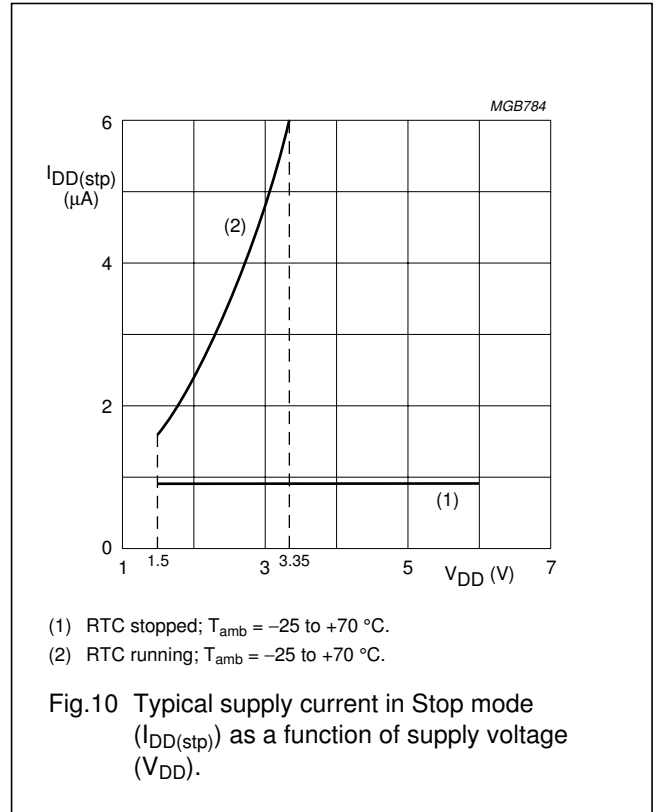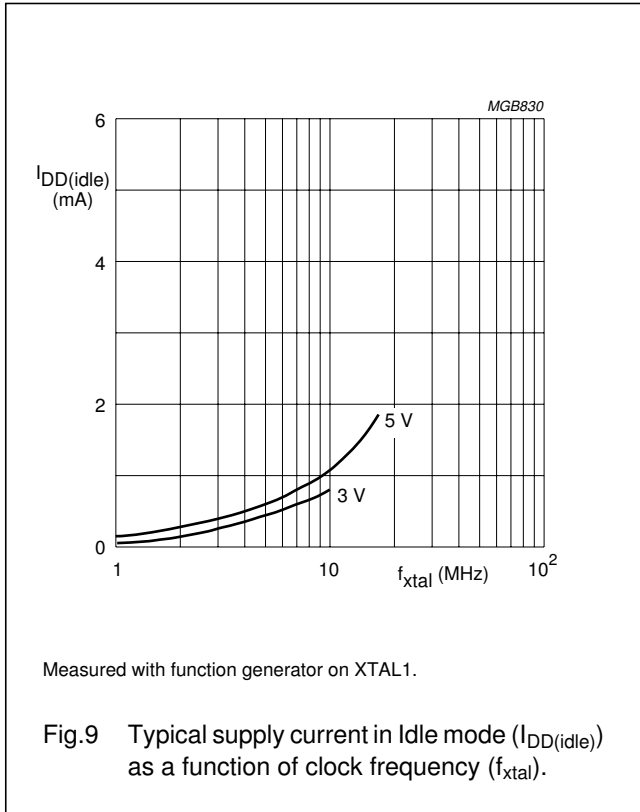function of clock frequency (f_{xtal}).

Measured with crystal between XTAL1 and XTAL2.

Fig.8   Typical supply current in Idle mode ($I_{DD(idle)}$)
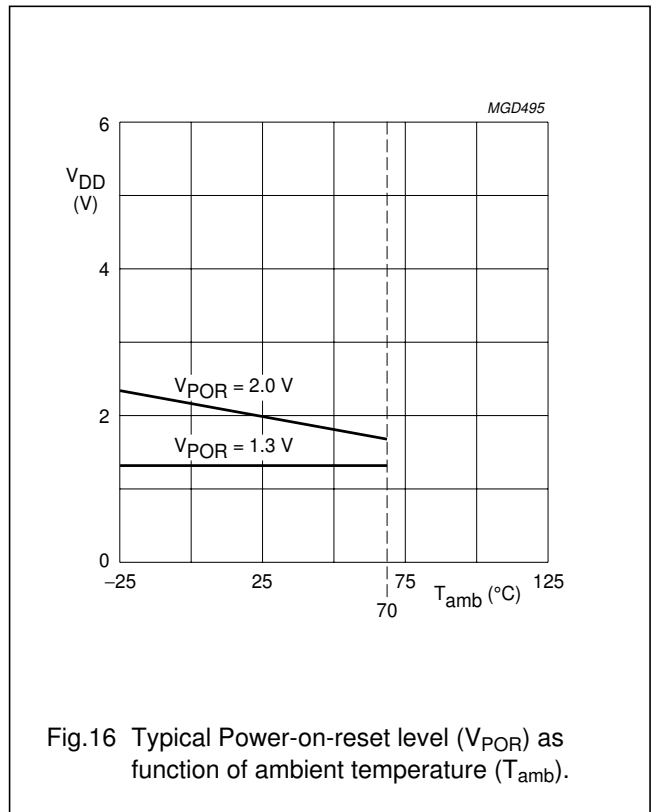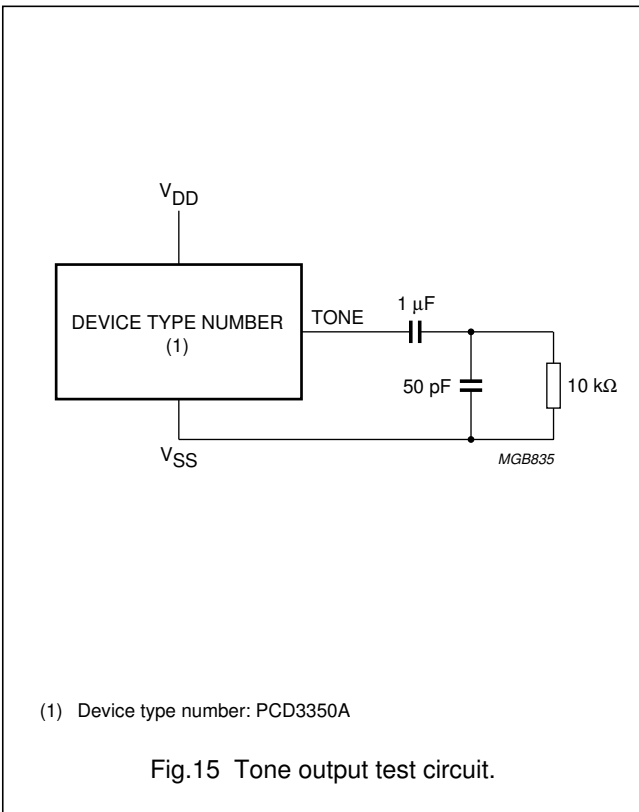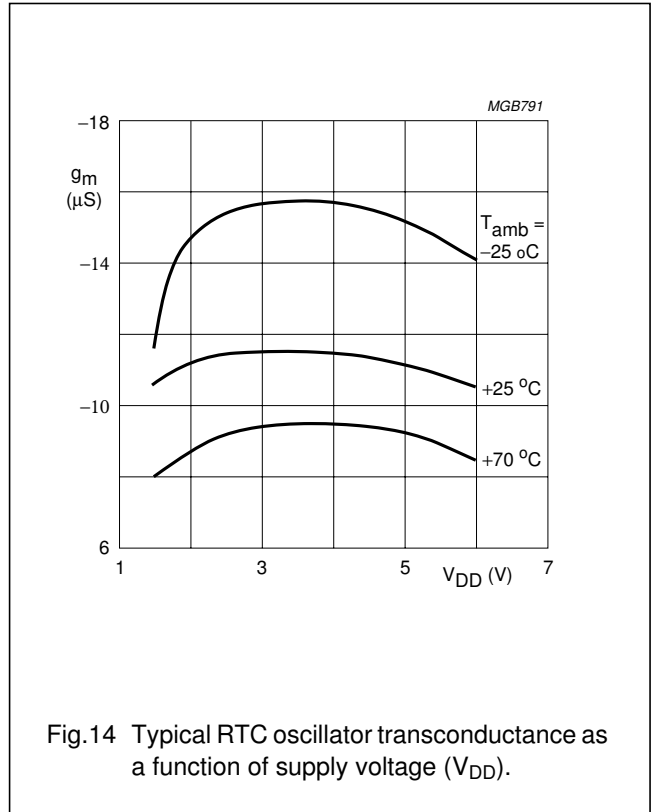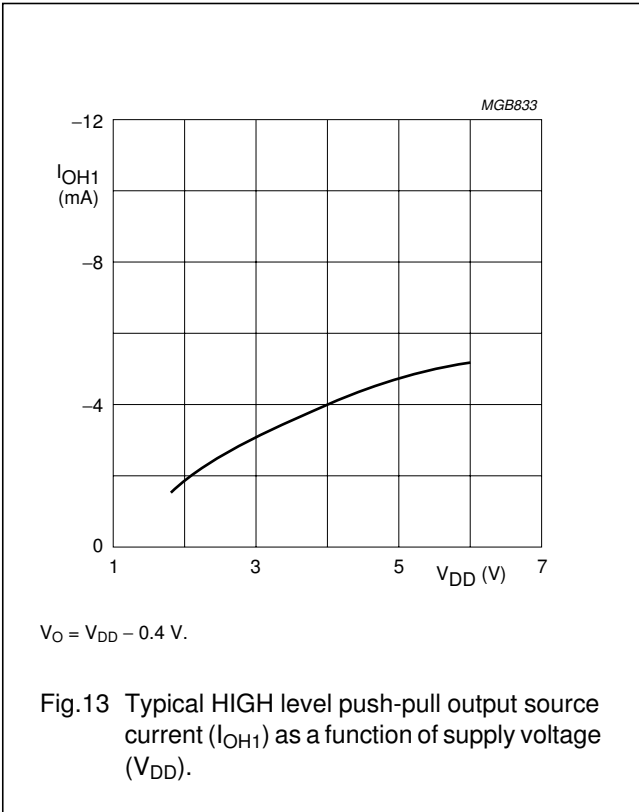as a function of supply voltage (V_{DD}).

Measured with function generator on XTAL1.

Fig.9 Typical supply current in Idle mode ($I_{DD(idle)}$) as a function of clock frequency (f_{xtal}).

(1) RTC stopped; T_{amb} = −25 to +70 °C.
(2) RTC running; T_{amb} = −25 to +70 °C.

Fig.10 Typical supply current in Stop mode ($I_{DD(stp)}$) as a function of supply voltage (V_{DD}).

V_O = 0.4 V.

Fig.11 Typical LOW level output sink current (I_{OL}) as a function of supply voltage (V_{DD}).

Fig.12 Typical HIGH level pull-up output source current (I_{OH}) as a function of supply voltage (V_{DD}).

8-bit microcontroller with DTMF generator,
256 bytes EEPROM and real-time clock

PCD3350A

$V_O = V_{DD} - 0.4$ V.

Fig.13 Typical HIGH level push-pull output source
current (I_{OH1}) as a function of supply voltage
(V_{DD}).

Fig.14 Typical RTC oscillator transconductance as
a function of supply voltage (V_{DD}).

(1) Device type number: PCD3350A

Fig.15 Tone output test circuit.

Fig.16 Typical Power-on-reset level (V_{POR}) as
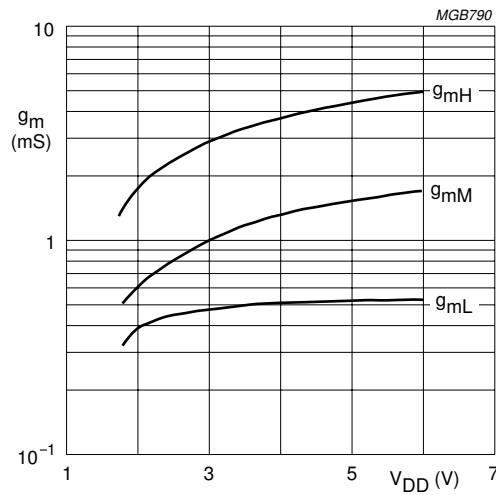function of ambient temperature (T_{amb}).

Fig.17 Typical oscillator transconductance (g_m) as a function of supply voltage (V_{DD}).

19 AC CHARACTERISTICS

V_{DD} = 1.8 to 6 V; V_{SS} = 0 V; T_{amb} = −25 to +70 °C; all voltages with respect to V_{SS}; unless otherwise specified.

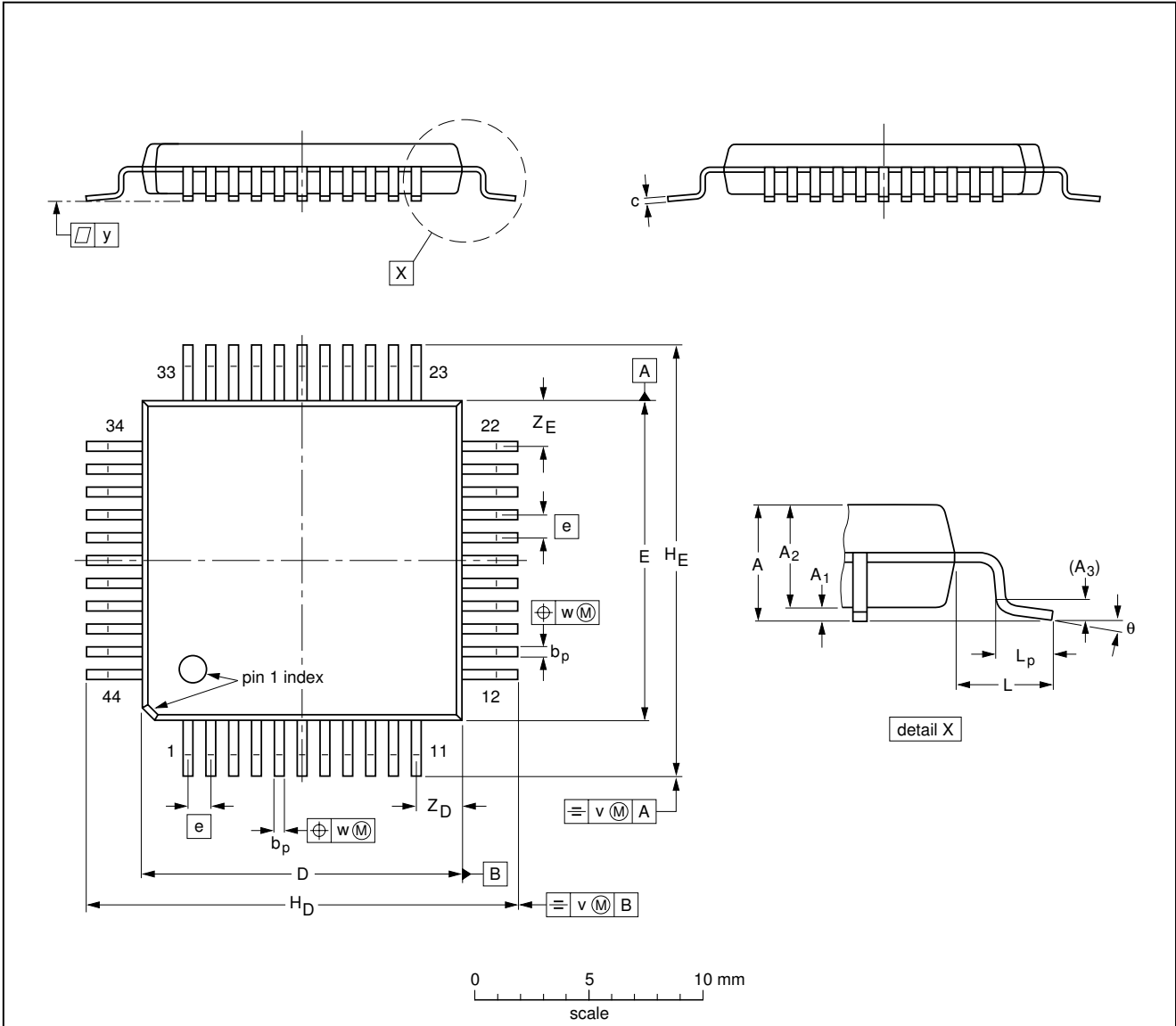| SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
t_r	rise time all outputs	V_{DD} = 5 V; T_{amb} = 25 °C; C_L = 50 pF	–	30	–	ns
t_f	fall time all outputs		–	30	–	ns
f_{xtal}	clock frequency	see Fig.5	1	–	16	MHz

8-bit microcontroller with DTMF generator, 256 bytes EEPROM and real-time clock

PCD3350A

20 PACKAGE OUTLINE

QFP44: plastic quad flat package; 44 leads (lead length 2.35 mm); body 14 x 14 x 2.2 mm   **SOT205-1**

DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A₁	A₂	A₃	b_p	c	D(1)	E(1)	e	H_D	H_E	L	L_p	v	w	y	Z_D(1)	Z_E(1)	θ
mm	2.60	0.25 0.05	2.3 2.1	0.25	0.50 0.35	0.25 0.14	14.1 13.9	14.1 13.9	1	19.2 18.2	19.2 18.2	2.35	2.0 1.2	0.3	0.15	0.1	2.4 1.8	2.4 1.8	7° 0°

Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT205-1	133E01A					~~95-02-04~~ 97-08-01

21   SOLDERING

21.1   Introduction

There is no soldering method that is ideal for all IC packages. Wave soldering is often preferred when through-hole and surface mounted components are mixed on one printed-circuit board. However, wave soldering is not always suitable for surface mounted ICs, or for printed-circuits with high population densities. In these situations reflow soldering is often used.

This text gives a very brief insight to a complex technology. A more in-depth account of soldering ICs can be found in our *"IC Package Databook"* (order code 9398 652 90011).

21.2   Reflow soldering

Reflow soldering techniques are suitable for all QFP packages.

The choice of heating method may be influenced by larger plastic QFP packages (44 leads, or more). If infrared or vapour phase heating is used and the large packages are not absolutely dry (less than 0.1% moisture content by weight), vaporization of the small amount of moisture in them can cause cracking of the plastic body. For more information, refer to the Drypack chapter in our *"Quality Reference Handbook"* (order code 9397 750 00192).

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stencilling or pressure-syringe dispensing before package placement.

Several techniques exist for reflowing; for example, thermal conduction by heated belt. Dwell times vary between 50 and 300 seconds depending on heating method. Typical reflow temperatures range from 215 to 250 °C.

Preheating is necessary to dry the paste and evaporate the binding agent. Preheating duration: 45 minutes at 45 °C.

21.3   Wave soldering

Wave soldering is **not** recommended for QFP packages. This is because of the likelihood of solder bridging due to closely-spaced leads and the possibility of incomplete solder penetration in multi-lead devices.

If wave soldering cannot be avoided, the following conditions must be observed:

- **A double-wave (a turbulent wave with high upward pressure followed by a smooth laminar wave) soldering technique should be used.**
- **The footprint must be at an angle of 45° to the board direction and must incorporate solder thieves downstream and at the side corners.**

Even with these conditions, do not consider wave soldering the following packages: QFP52 (SOT379-1), QFP100 (SOT317-1), QFP100 (SOT317-2), QFP100 (SOT382-1) or QFP160 (SOT322-1).

During placement and before soldering, the package must be fixed with a droplet of adhesive. The adhesive can be applied by screen printing, pin transfer or syringe dispensing. The package can be soldered after the adhesive is cured.

Maximum permissible solder temperature is 260 °C, and maximum duration of package immersion in solder is 10 seconds, if cooled to less than 150 °C within 6 seconds. Typical dwell time is 4 seconds at 250 °C.

A mildly-activated flux will eliminate the need for removal of corrosive residues in most applications.

21.4   Repairing soldered joints

Fix the component by first soldering two diagonally-opposite end leads. Use only a low voltage soldering iron (less than 24 V) applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to 300 °C. When using a dedicated tool, all other leads can be soldered in one operation within 2 to 5 seconds between 270 and 320 °C.

22 DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

23 LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

Philips Semiconductors – a worldwide company

Argentina: see South America

Australia: 34 Waterloo Road, NORTH RYDE, NSW 2113,
Tel. +61 2 9805 4455, Fax. +61 2 9805 4466

Austria: Computerstr. 6, A-1101 WIEN, P.O. Box 213,
Tel. +43 1 60 101, Fax. +43 1 60 101 1210

Belarus: Hotel Minsk Business Center, Bld. 3, r. 1211, Volodarski Str. 6,
220050 MINSK, Tel. +375 172 200 733, Fax. +375 172 200 773

Belgium: see The Netherlands

Brazil: see South America

Bulgaria: Philips Bulgaria Ltd., Energoproject, 15th floor,
51 James Bourchier Blvd., 1407 SOFIA,
Tel. +359 2 689 211, Fax. +359 2 689 102

Canada: PHILIPS SEMICONDUCTORS/COMPONENTS,
Tel. +1 800 234 7381

China/Hong Kong: 501 Hong Kong Industrial Technology Centre,
72 Tat Chee Avenue, Kowloon Tong, HONG KONG,
Tel. +852 2319 7888, Fax. +852 2319 7700

Colombia: see South America

Czech Republic: see Austria

Denmark: Prags Boulevard 80, PB 1919, DK-2300 COPENHAGEN S,
Tel. +45 32 88 2636, Fax. +45 31 57 1949

Finland: Sinikalliontie 3, FIN-02630 ESPOO,
Tel. +358 9 615800, Fax. +358 9 61580/xxx

France: 4 Rue du Port-aux-Vins, BP317, 92156 SURESNES Cedex,
Tel. +33 1 40 99 6161, Fax. +33 1 40 99 6427

Germany: Hammerbrookstraße 69, D-20097 HAMBURG,
Tel. +49 40 23 53 60, Fax. +49 40 23 536 300

Greece: No. 15, 25th March Street, GR 17778 TAVROS/ATHENS,
Tel. +30 1 4894 339/239, Fax. +30 1 4814 240

Hungary: see Austria

India: Philips INDIA Ltd, Shivsagar Estate, A Block, Dr. Annie Besant Rd.
Worli, MUMBAI 400 018, Tel. +91 22 4938 541, Fax. +91 22 4938 722

Indonesia: see Singapore

Ireland: Newstead, Clonskeagh, DUBLIN 14,
Tel. +353 1 7640 000, Fax. +353 1 7640 200

Israel: RAPAC Electronics, 7 Kehilat Saloniki St, TEL AVIV 61180,
Tel. +972 3 645 0444, Fax. +972 3 649 1007

Italy: PHILIPS SEMICONDUCTORS, Piazza IV Novembre 3,
20124 MILANO, Tel. +39 2 6752 2531, Fax. +39 2 6752 2557

Japan: Philips Bldg 13-37, Kohnan 2-chome, Minato-ku, TOKYO 108,
Tel. +81 3 3740 5130, Fax. +81 3 3740 5077

Korea: Philips House, 260-199 Itaewon-dong, Yongsan-ku, SEOUL,
Tel. +82 2 709 1412, Fax. +82 2 709 1415

Malaysia: No. 76 Jalan Universiti, 46200 PETALING JAYA, SELANGOR,
Tel. +60 3 750 5214, Fax. +60 3 757 4880

Mexico: 5900 Gateway East, Suite 200, EL PASO, TEXAS 79905,
Tel. +9-5 800 234 7381

Middle East: see Italy

Netherlands: Postbus 90050, 5600 PB EINDHOVEN, Bldg. VB,
Tel. +31 40 27 82785, Fax. +31 40 27 88399

New Zealand: 2 Wagener Place, C.P.O. Box 1041, AUCKLAND,
Tel. +64 9 849 4160, Fax. +64 9 849 7811

Norway: Box 1, Manglerud 0612, OSLO,
Tel. +47 22 74 8000, Fax. +47 22 74 8341

Philippines: Philips Semiconductors Philippines Inc.,
106 Valero St. Salcedo Village, P.O. Box 2108 MCC, MAKATI,
Metro MANILA, Tel. +63 2 816 6380, Fax. +63 2 817 3474

Poland: Ul. Lukiska 10, PL 04-123 WARSZAWA,
Tel. +48 22 612 2831, Fax. +48 22 612 2327

Portugal: see Spain

Romania: see Italy

Russia: Philips Russia, Ul. Usatcheva 35A, 119048 MOSCOW,
Tel. +7 095 247 9145, Fax. +7 095 247 9144

Singapore: Lorong 1, Toa Payoh, SINGAPORE 1231,
Tel. +65 350 2538, Fax. +65 251 6500

Slovakia: see Austria

Slovenia: see Italy

South Africa: S.A. PHILIPS Pty Ltd., 195-215 Main Road Martindale,
2092 JOHANNESBURG, P.O. Box 7430 Johannesburg 2000,
Tel. +27 11 470 5911, Fax. +27 11 470 5494

South America: Rua do Rocio 220, 5th floor, Suite 51,
04552-903 São Paulo, SÃO PAULO - SP, Brazil,
Tel. +55 11 821 2333, Fax. +55 11 829 1849

Spain: Balmes 22, 08007 BARCELONA,
Tel. +34 3 301 6312, Fax. +34 3 301 4107

Sweden: Kottbygatan 7, Akalla, S-16485 STOCKHOLM,
Tel. +46 8 632 2000, Fax. +46 8 632 2745

Switzerland: Allmendstrasse 140, CH-8027 ZÜRICH,
Tel. +41 1 488 2686, Fax. +41 1 481 7730

Taiwan: PHILIPS TAIWAN Ltd., 23-30F, 66,
Chung Hsiao West Road, Sec. 1, P.O. Box 22978,
TAIPEI 100, Tel. +886 2 382 4443, Fax. +886 2 382 4444

Thailand: PHILIPS ELECTRONICS (THAILAND) Ltd.,
209/2 Sanpavuth-Bangna Road Prakanong, BANGKOK 10260,
Tel. +66 2 745 4090, Fax. +66 2 398 0793

Turkey: Talatpasa Cad. No. 5, 80640 GÜLTEPE/ISTANBUL,
Tel. +90 212 279 2770, Fax. +90 212 282 6707

Ukraine: PHILIPS UKRAINE, 4 Patrice Lumumba str., Building B, Floor 7,
252042 KIEV, Tel. +380 44 264 2776, Fax. +380 44 268 0461

United Kingdom: Philips Semiconductors Ltd., 276 Bath Road, Hayes,
MIDDLESEX UB3 5BX, Tel. +44 181 730 5000, Fax. +44 181 754 8421

United States: 811 East Arques Avenue, SUNNYVALE, CA 94088-3409,
Tel. +1 800 234 7381

Uruguay: see South America

Vietnam: see Singapore

Yugoslavia: PHILIPS, Trg N. Pasica 5/v, 11000 BEOGRAD,
Tel. +381 11 625 344, Fax.+381 11 635 777

For all other countries apply to: Philips Semiconductors, Marketing & Sales Communications,
Building BE-p, P.O. Box 218, 5600 MD EINDHOVEN, The Netherlands, Fax. +31 40 27 24825

Internet: http://www.semiconductors.philips.com

Printed in The Netherlands   417021/1200/04/pp36   Date of release: 1996 Dec 18   Document order number: 9397 750 01028

Let's make things better.

**Philips
Semiconductors**

PHILIPS